

(43) **Pub. Date:** **Aug. 21, 2025**

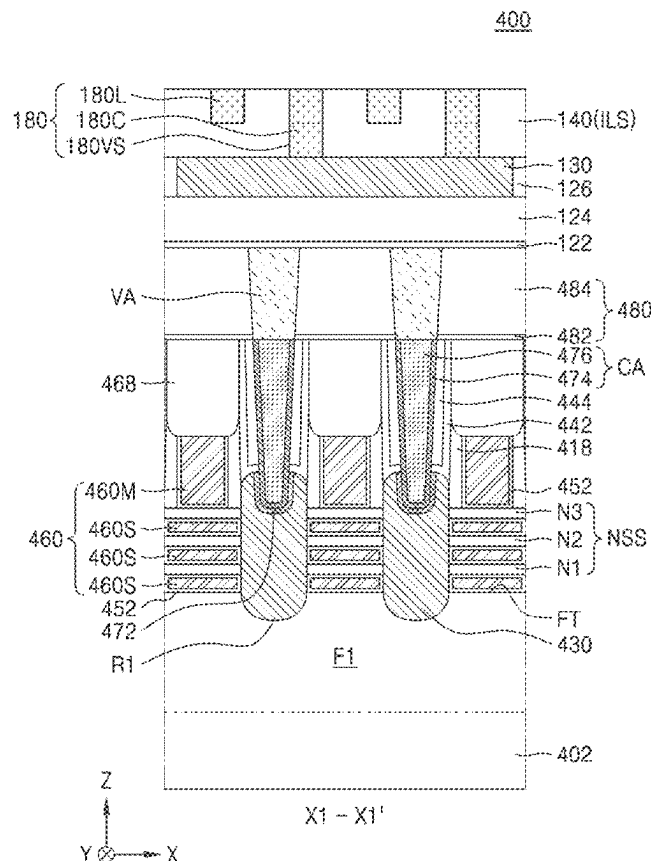


FIG. 1A

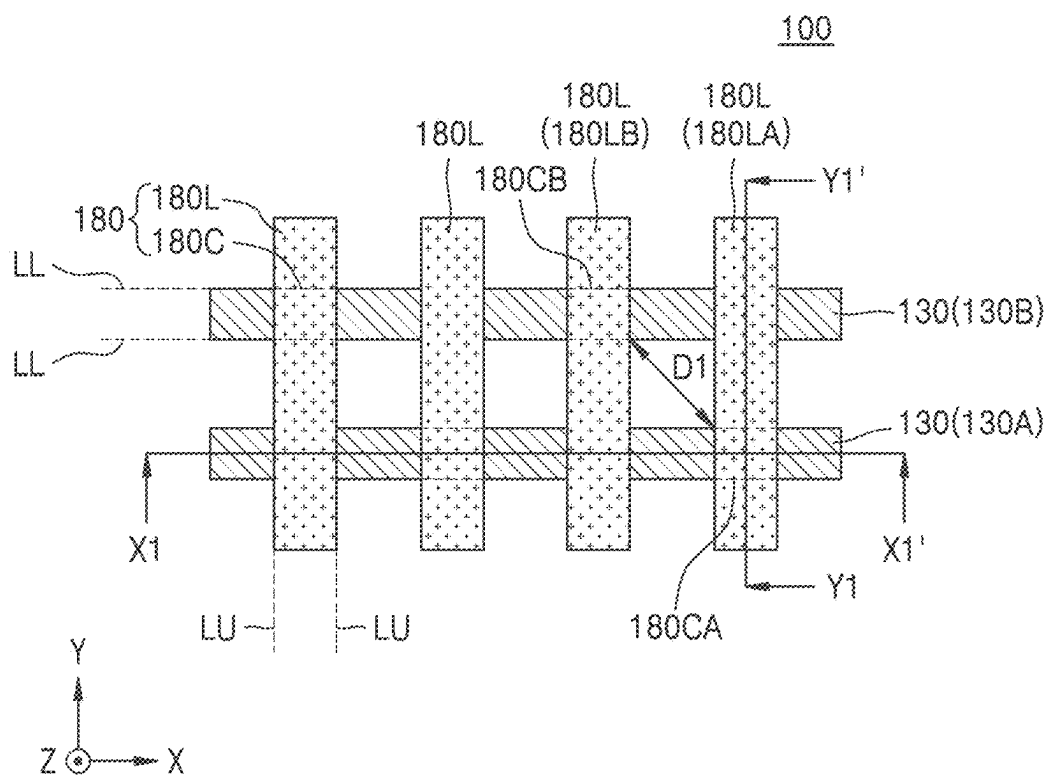


FIG. 1B

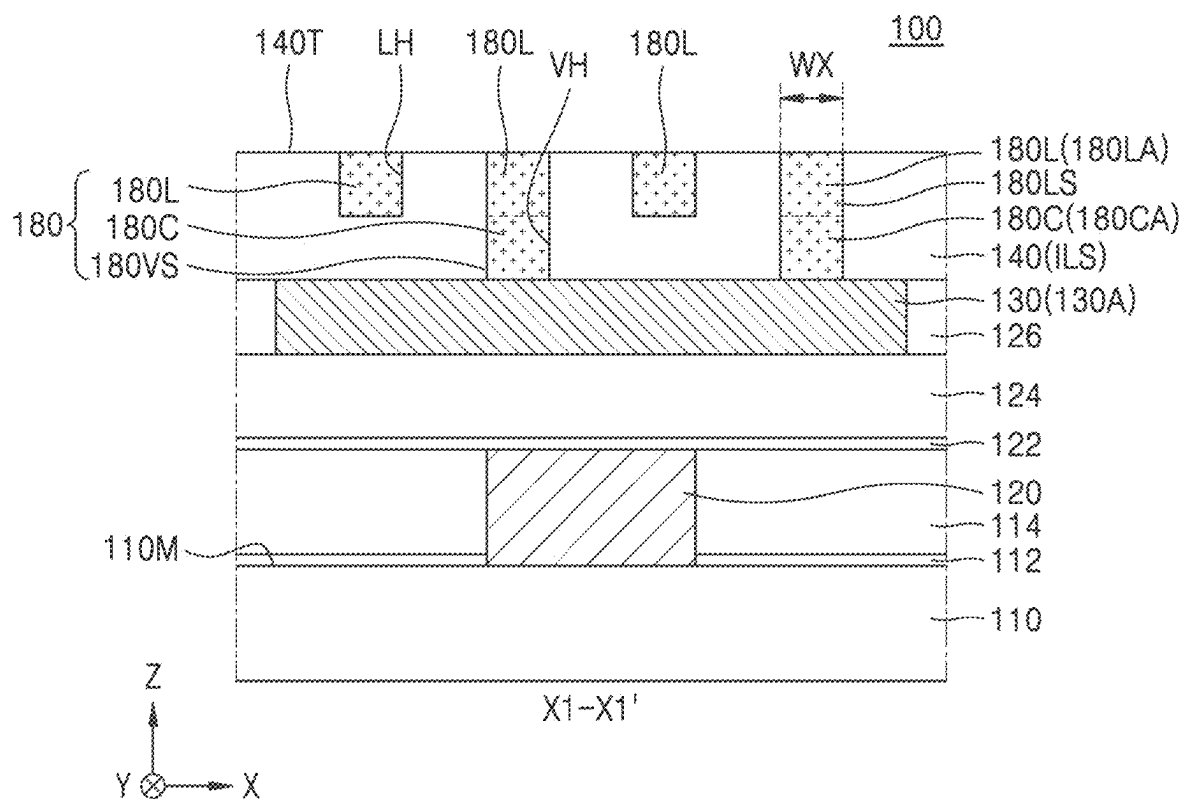


FIG. 1C

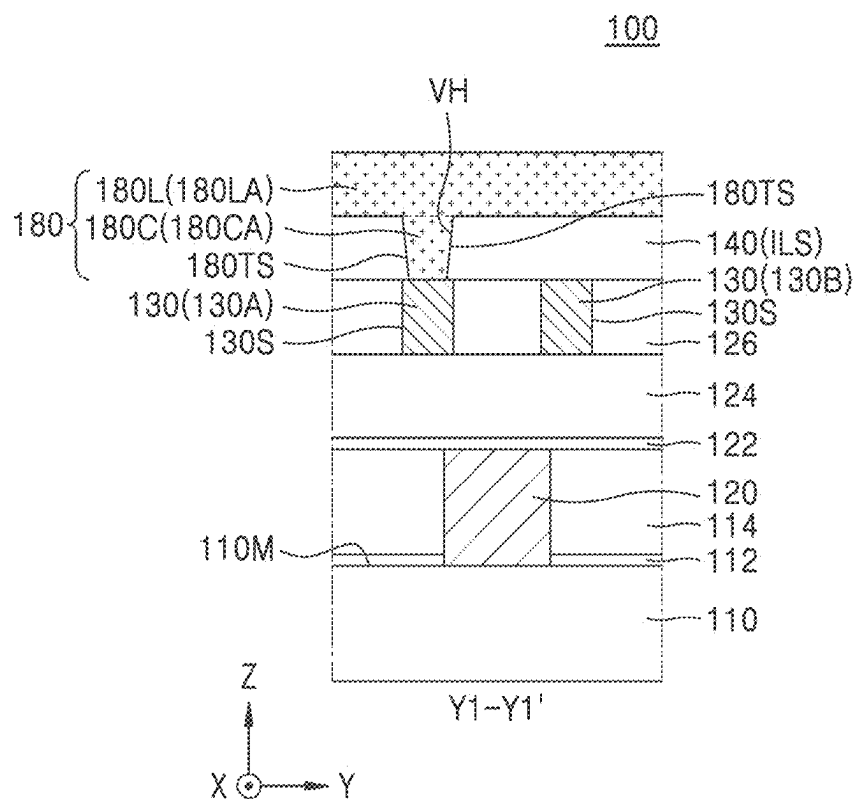


FIG. 2

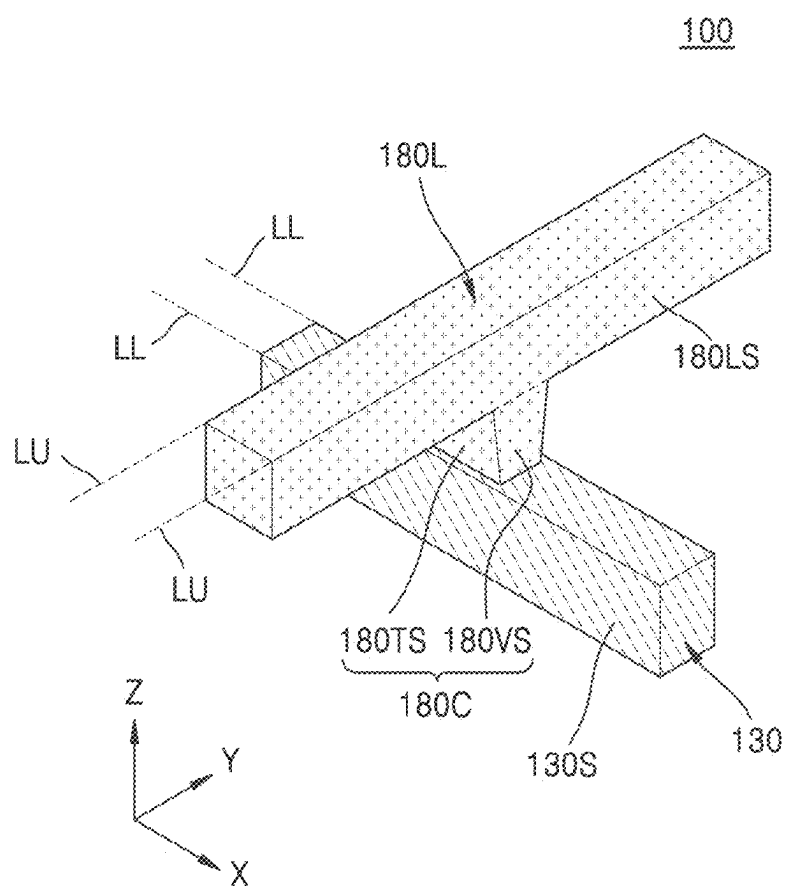


FIG. 3A

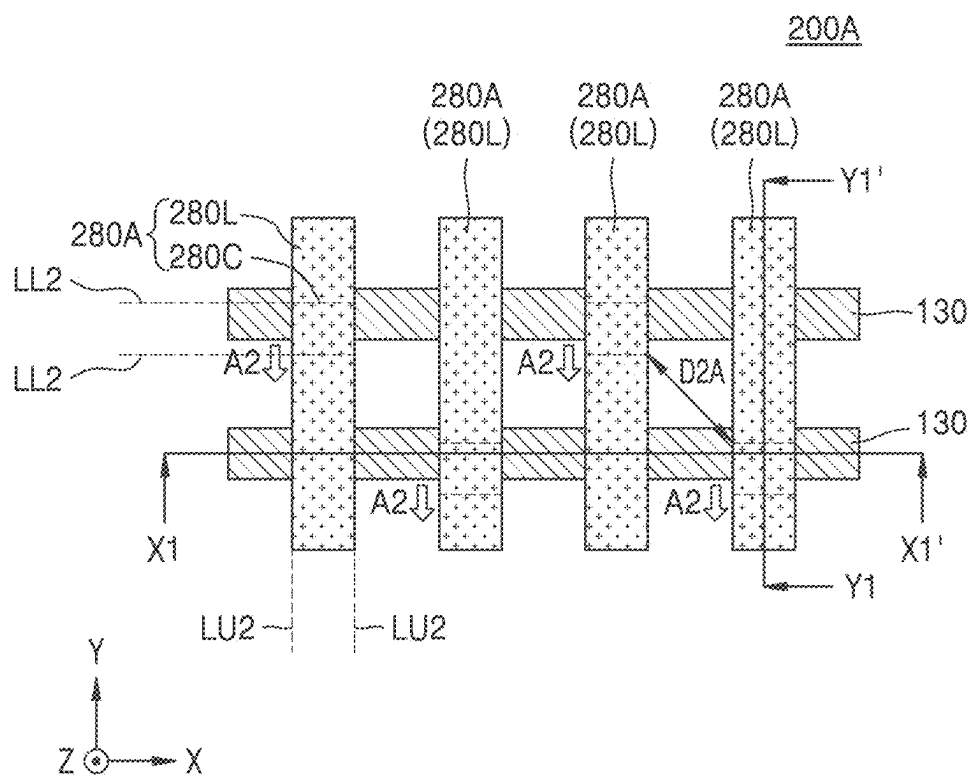


FIG. 3B

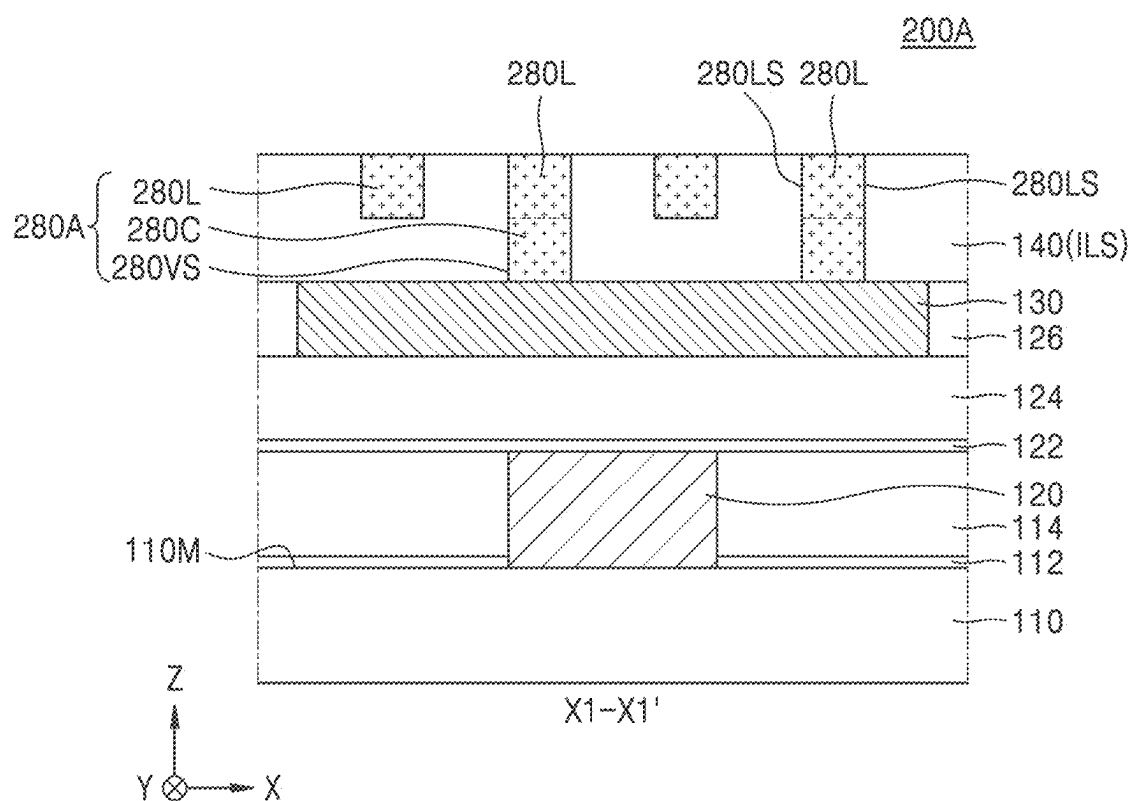


FIG. 3C

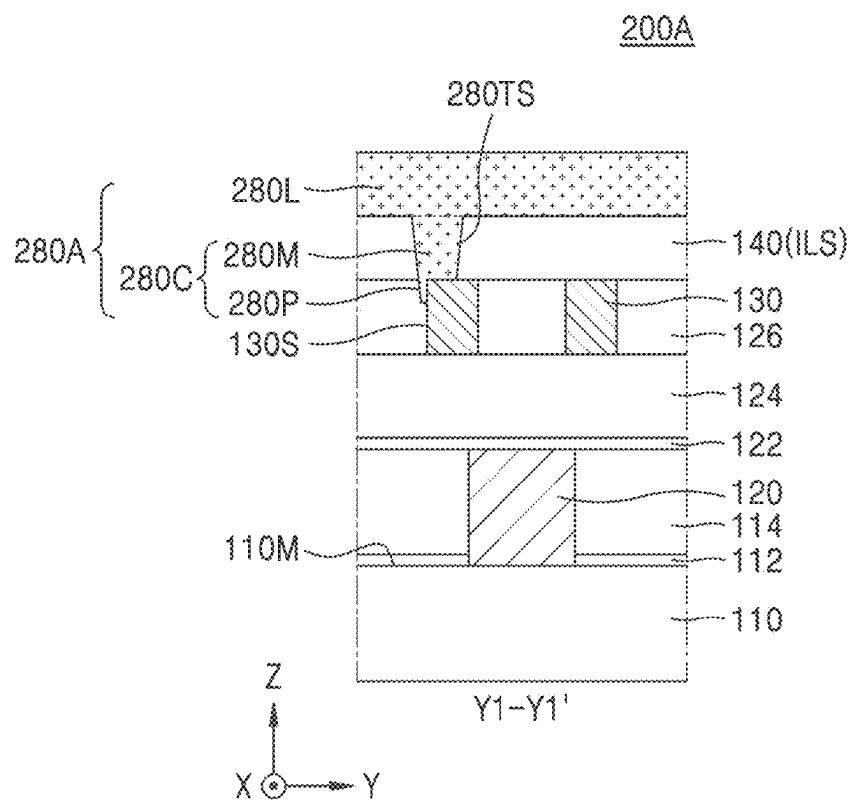




FIG. 4

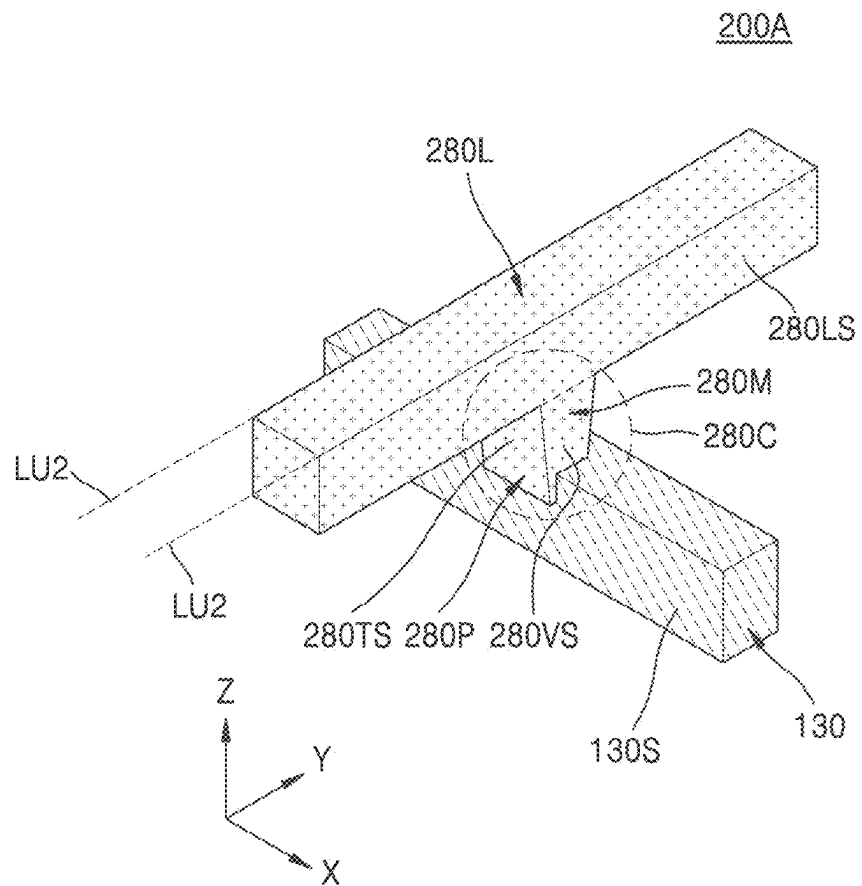


FIG. 5A

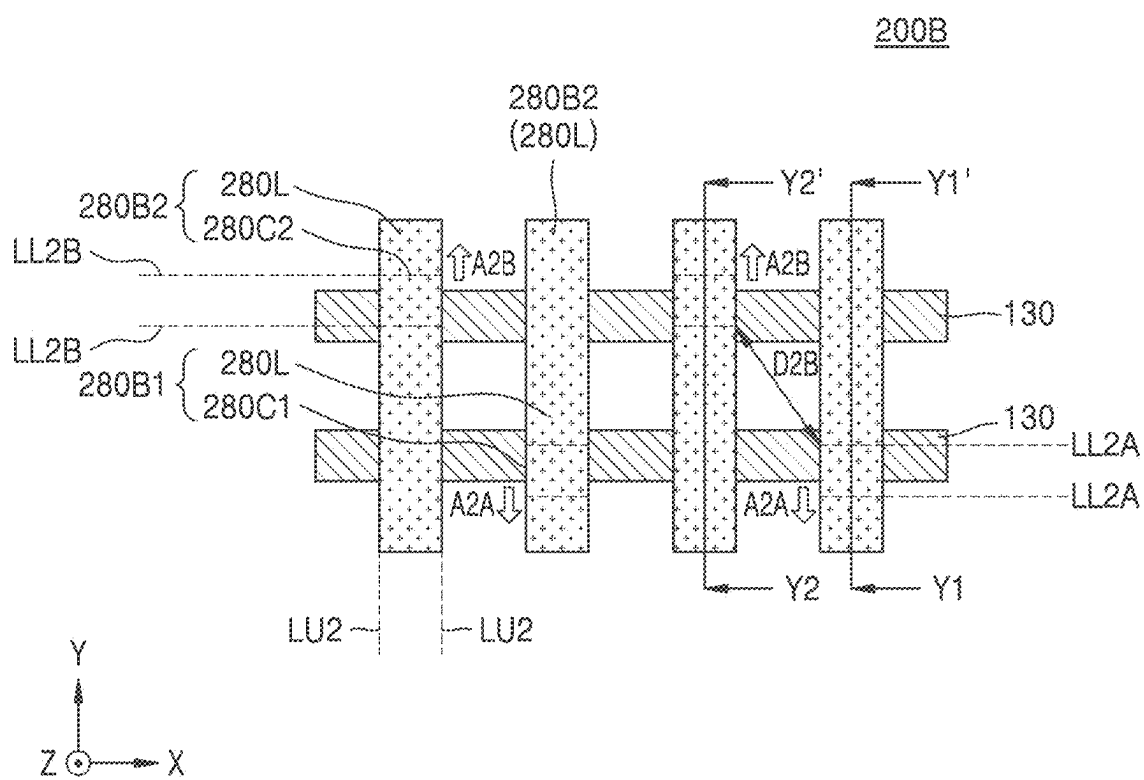


FIG. 5B

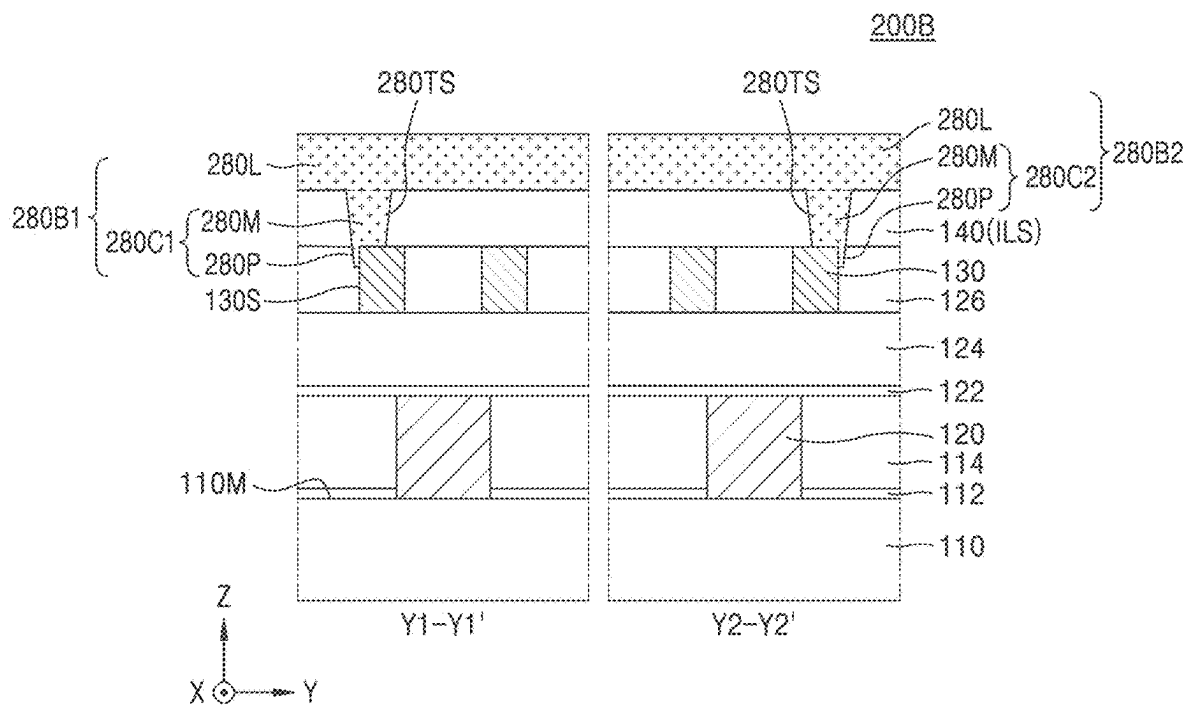


FIG. 6A

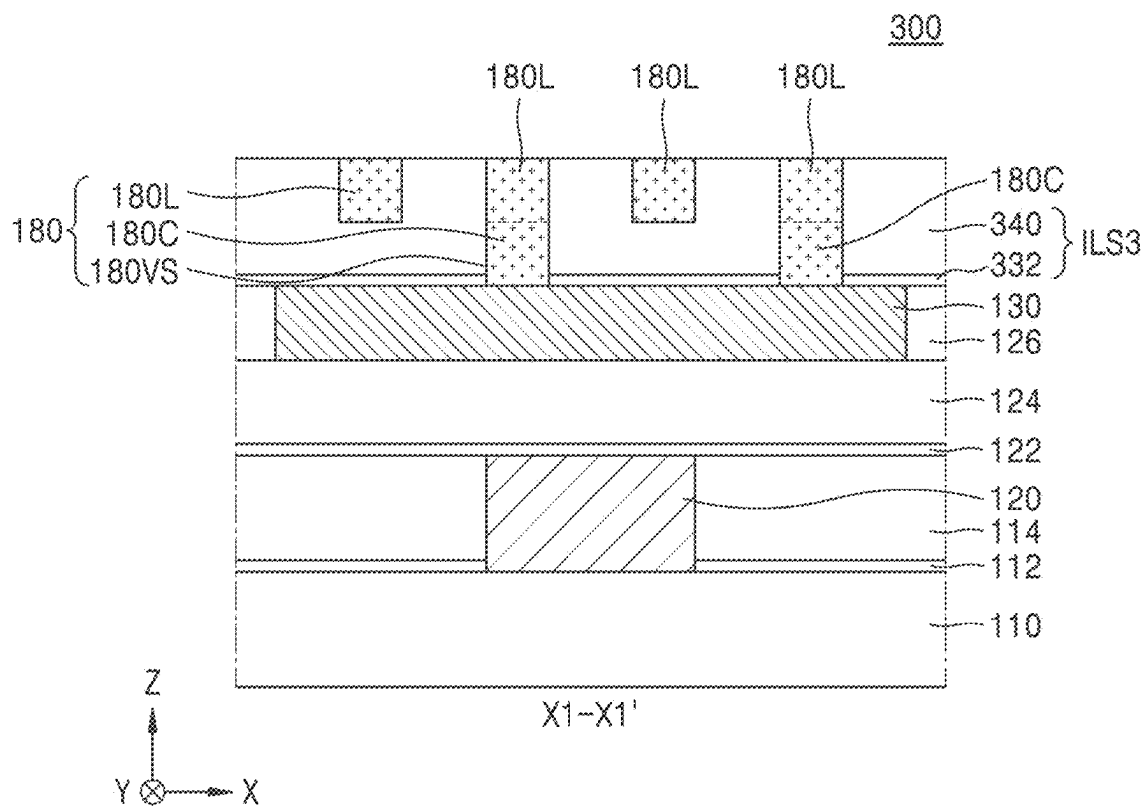


FIG. 6B

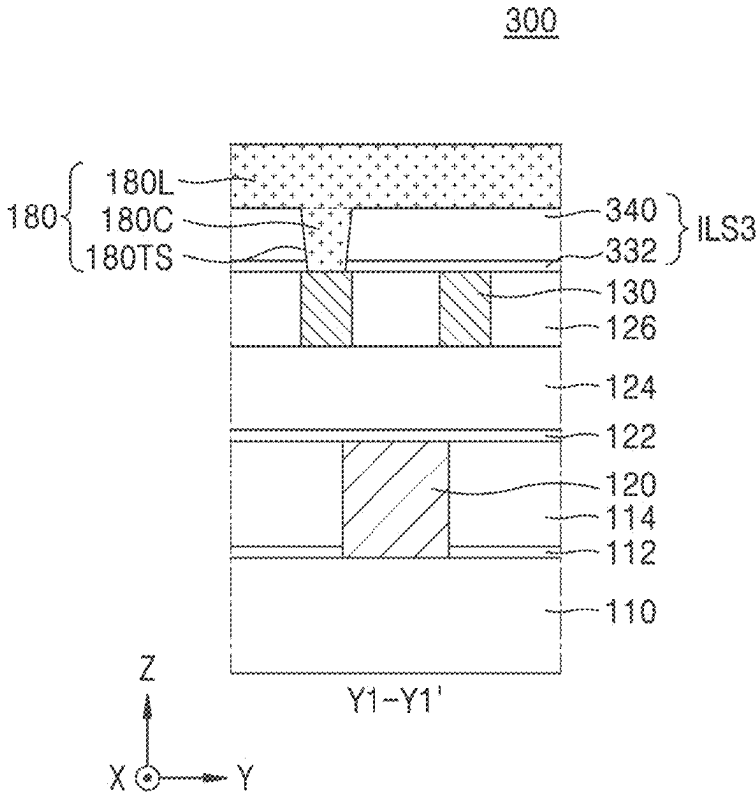


FIG. 7

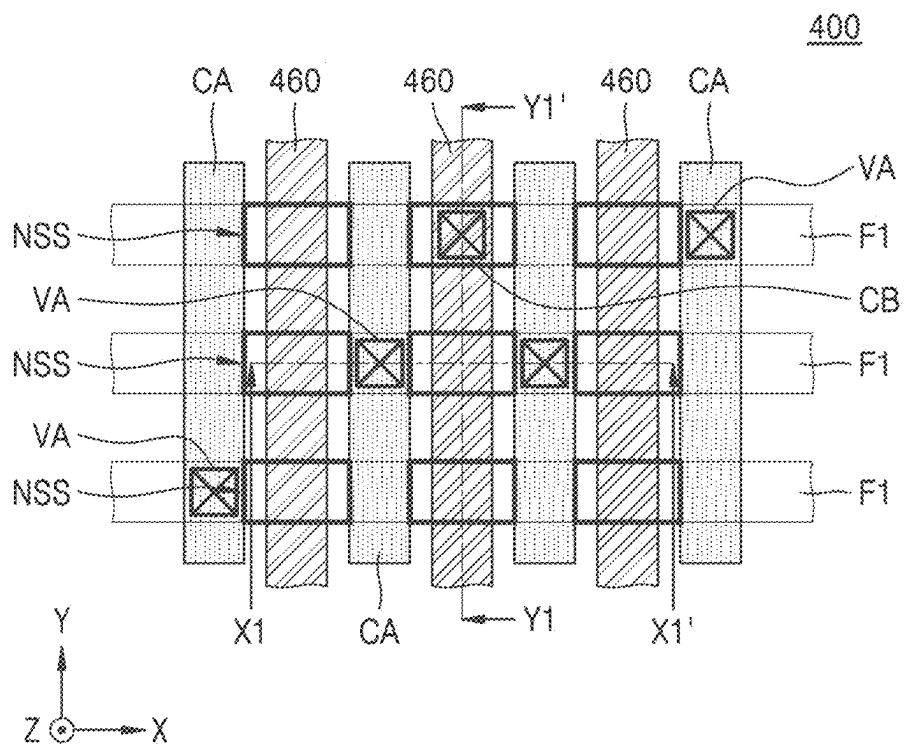


FIG. 8

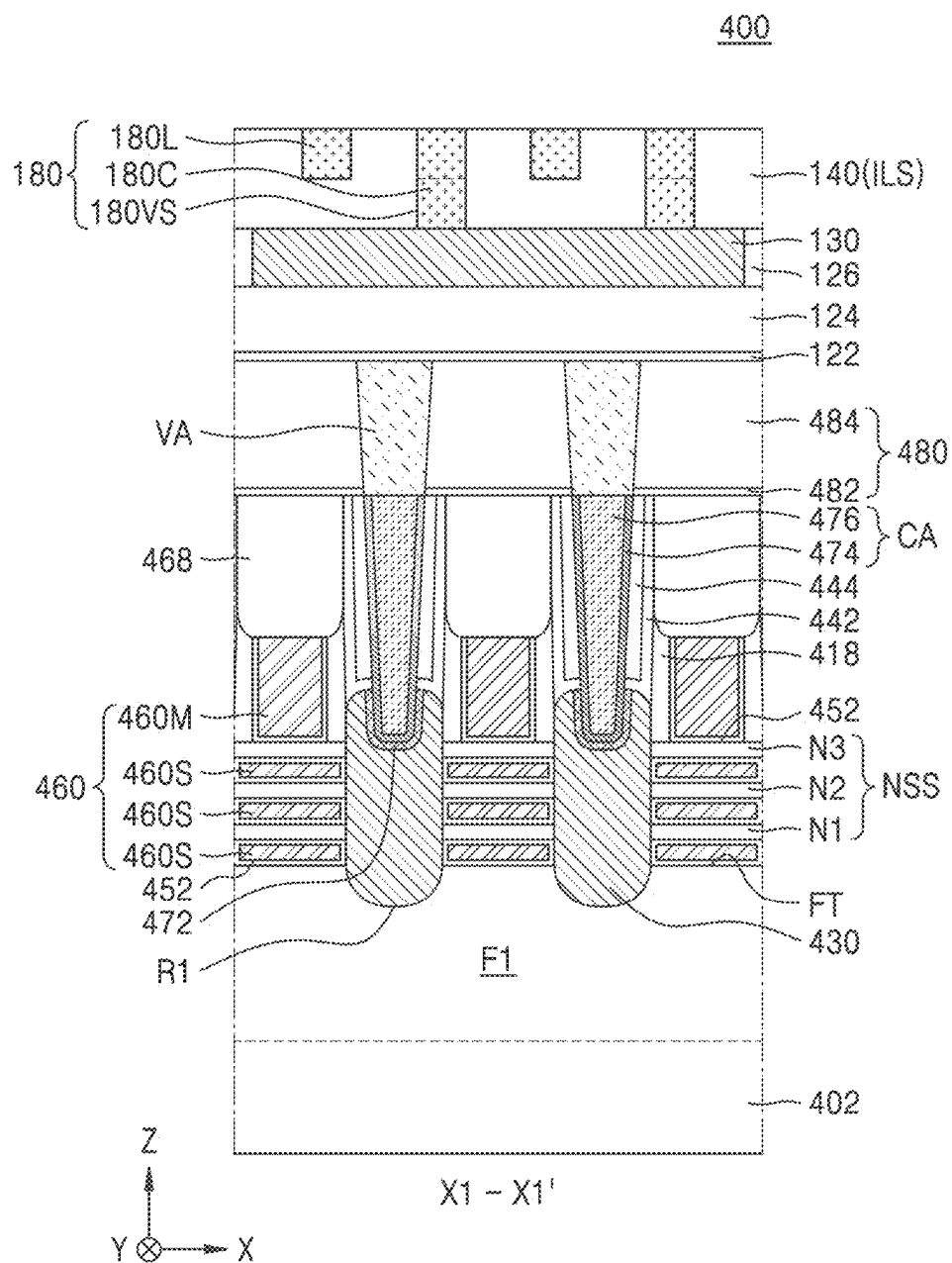


FIG. 9

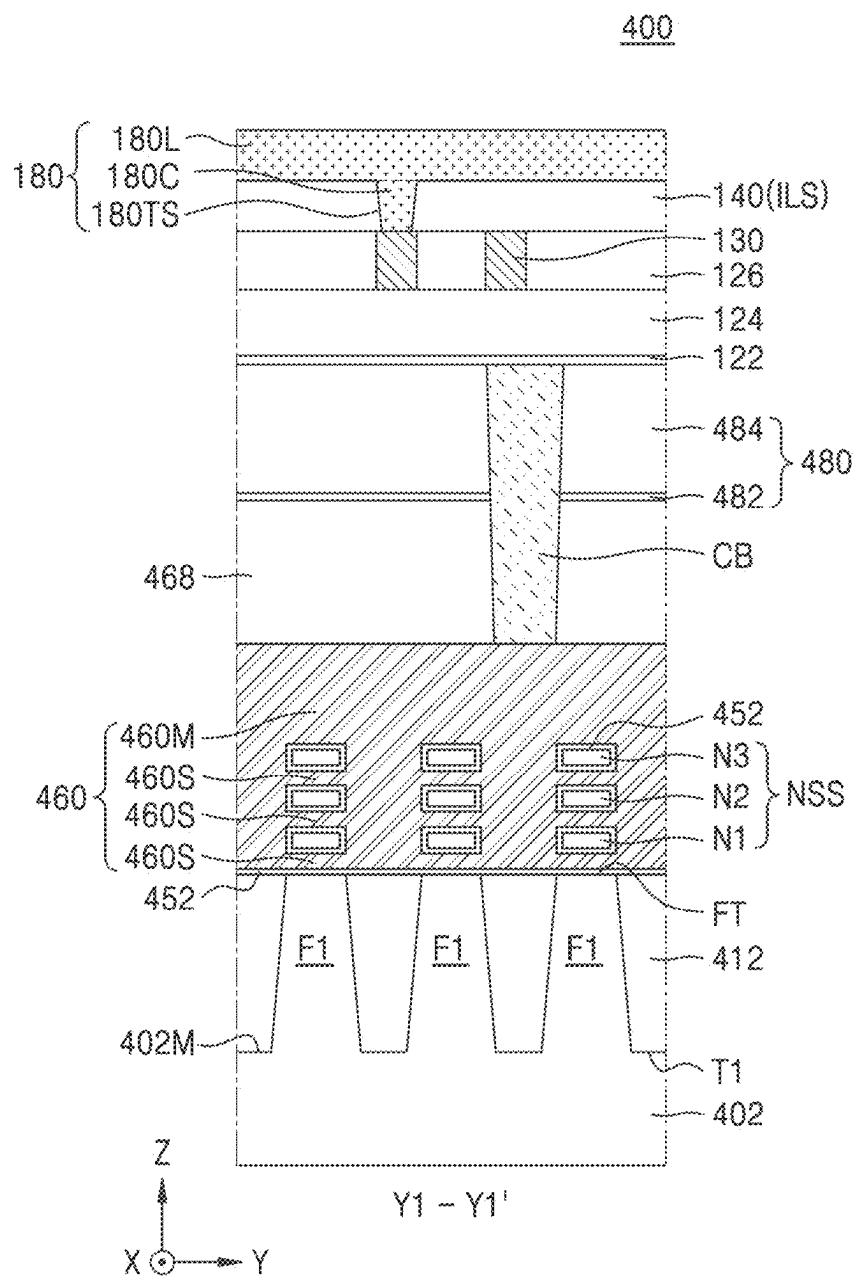




FIG. 10

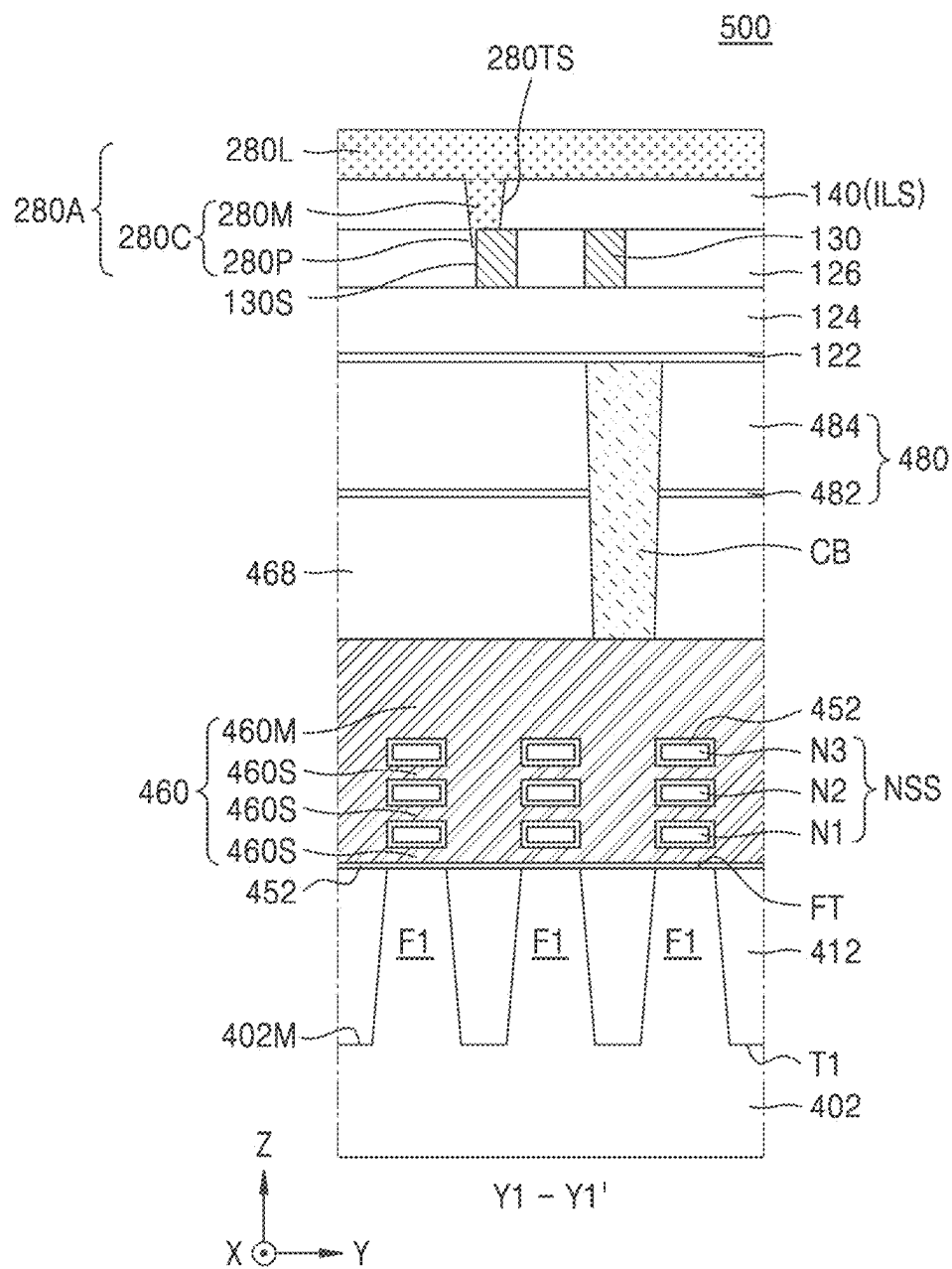


FIG. 11A

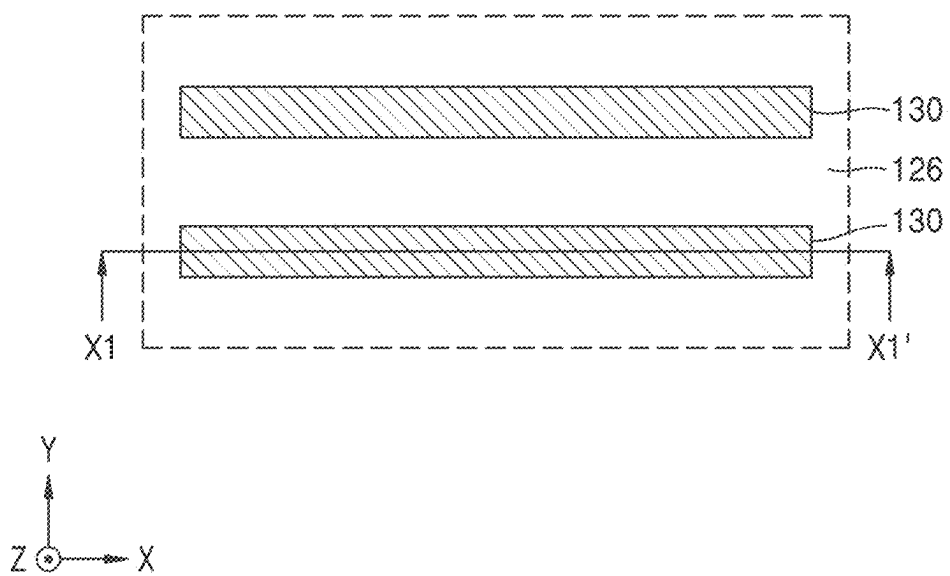


FIG. 11B

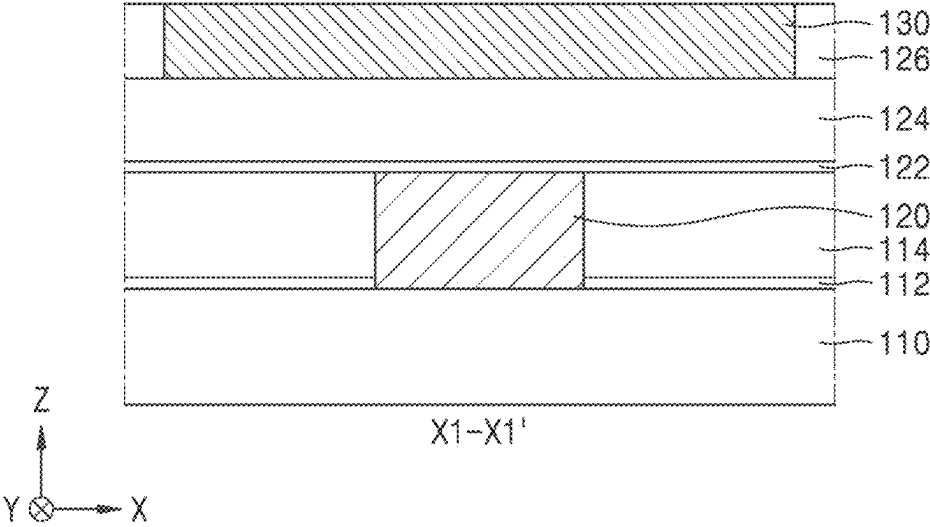


FIG. 12A

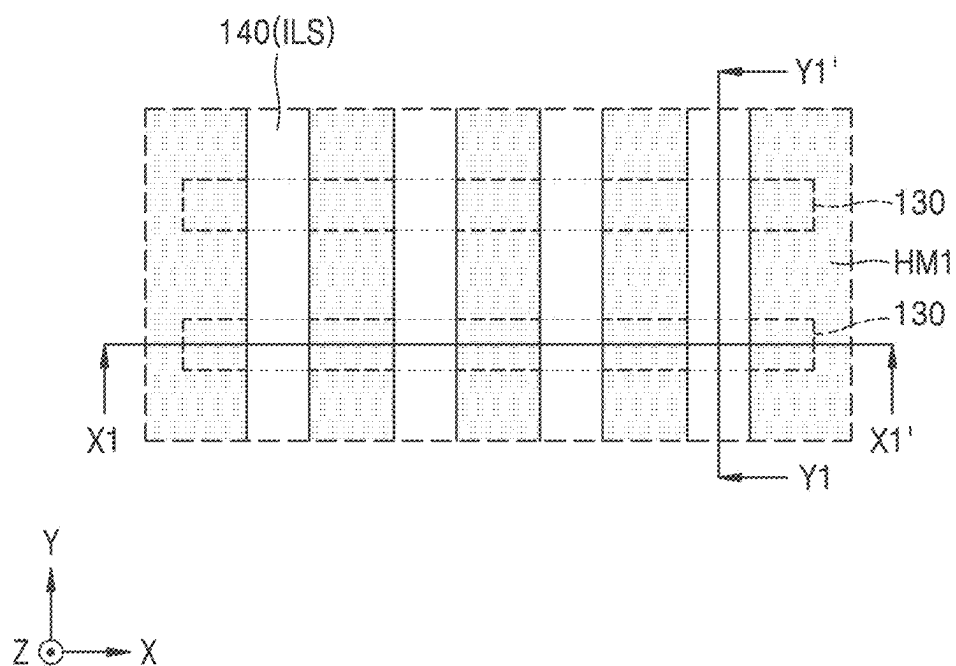


FIG. 12B

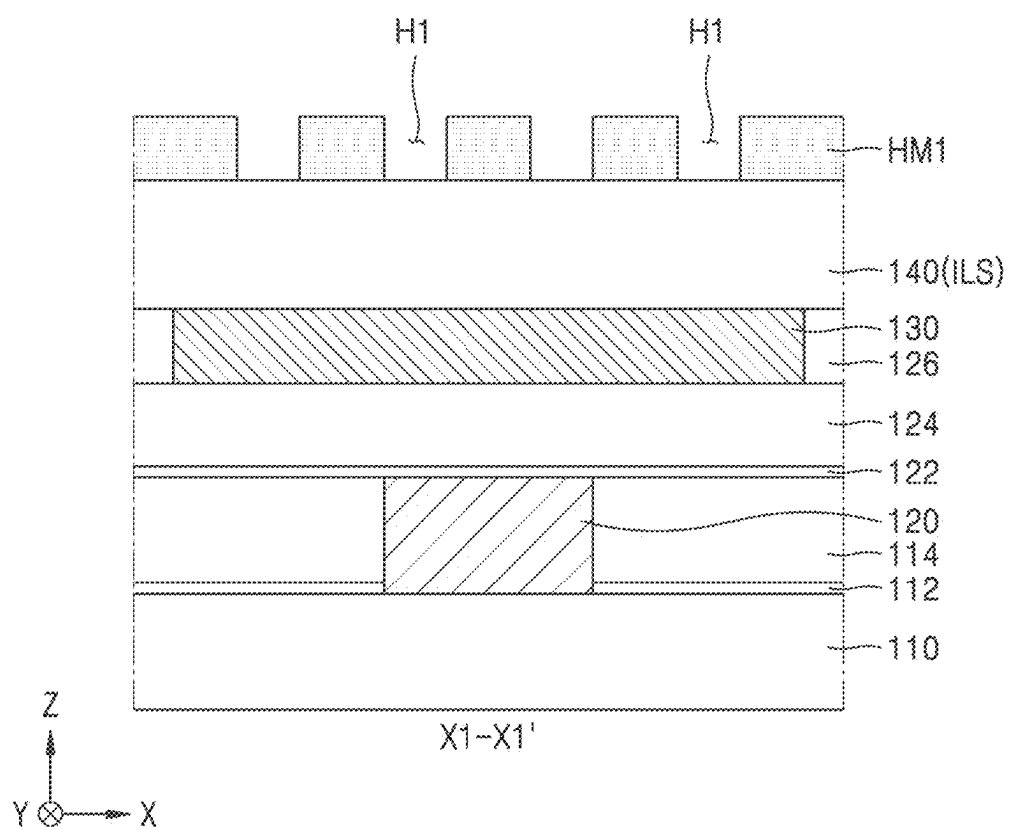


FIG. 13A

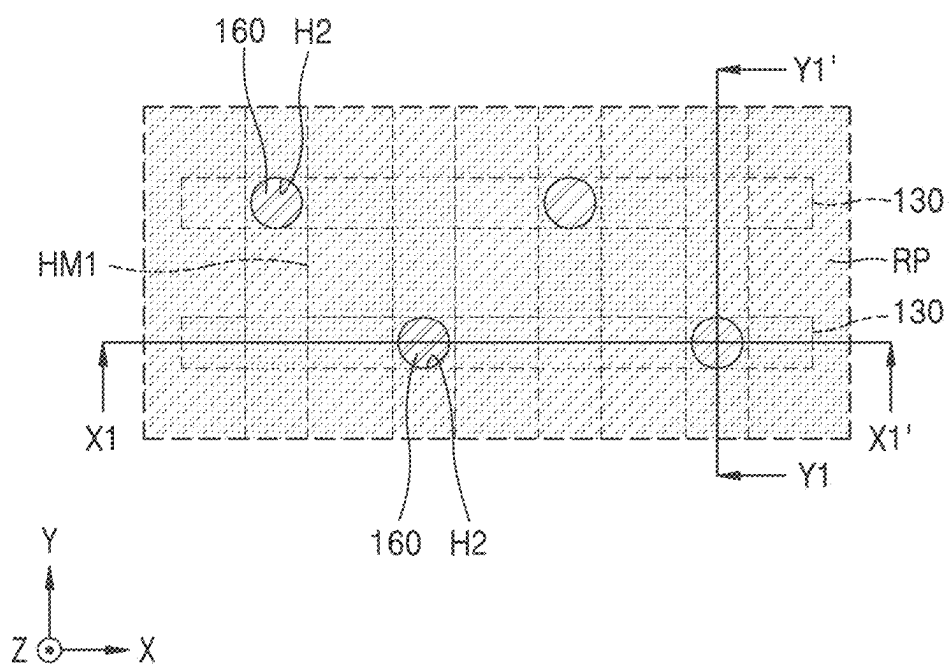


FIG. 13B

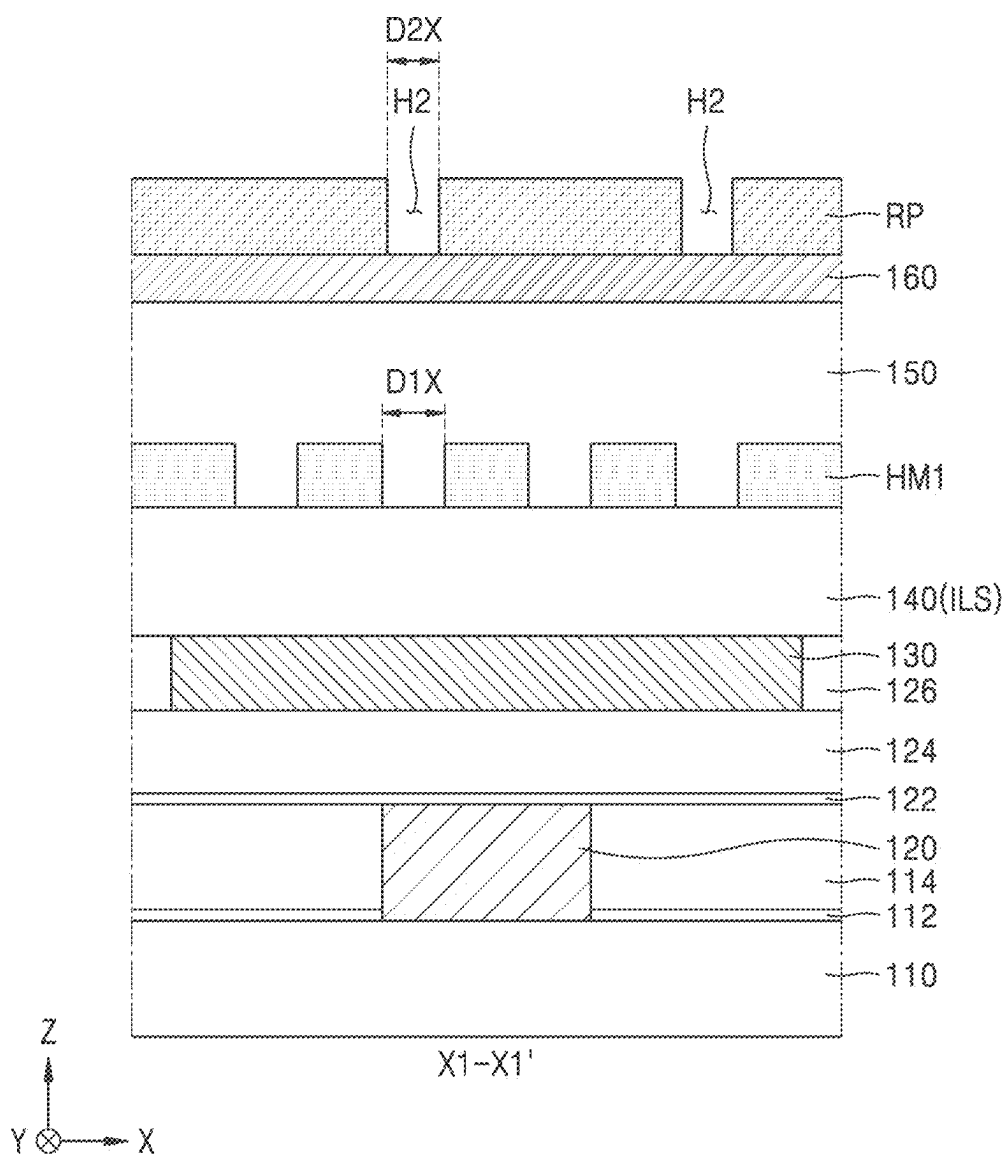


FIG. 14A

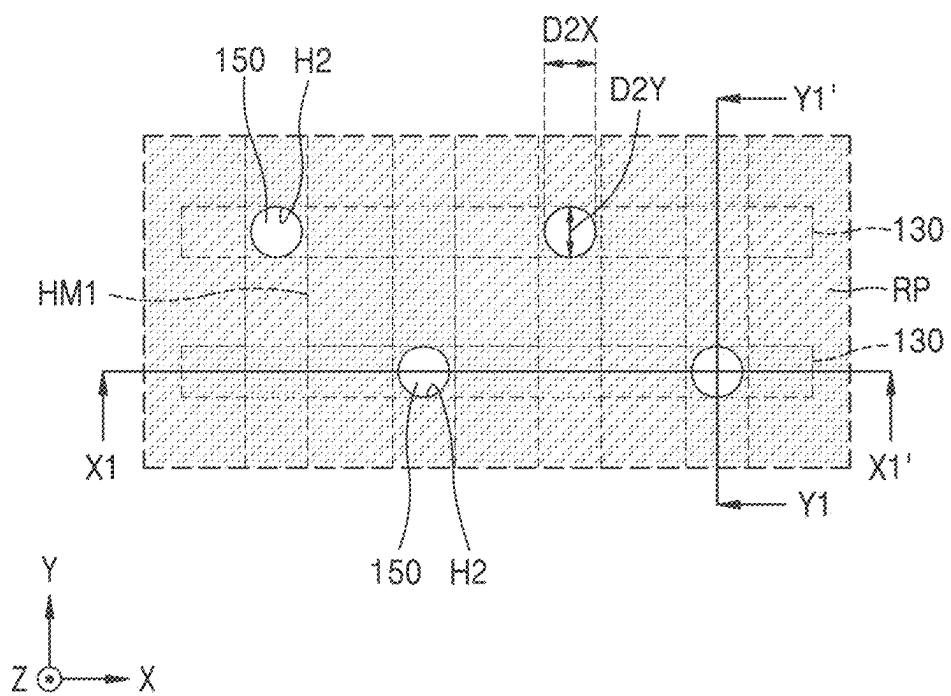




FIG. 14B

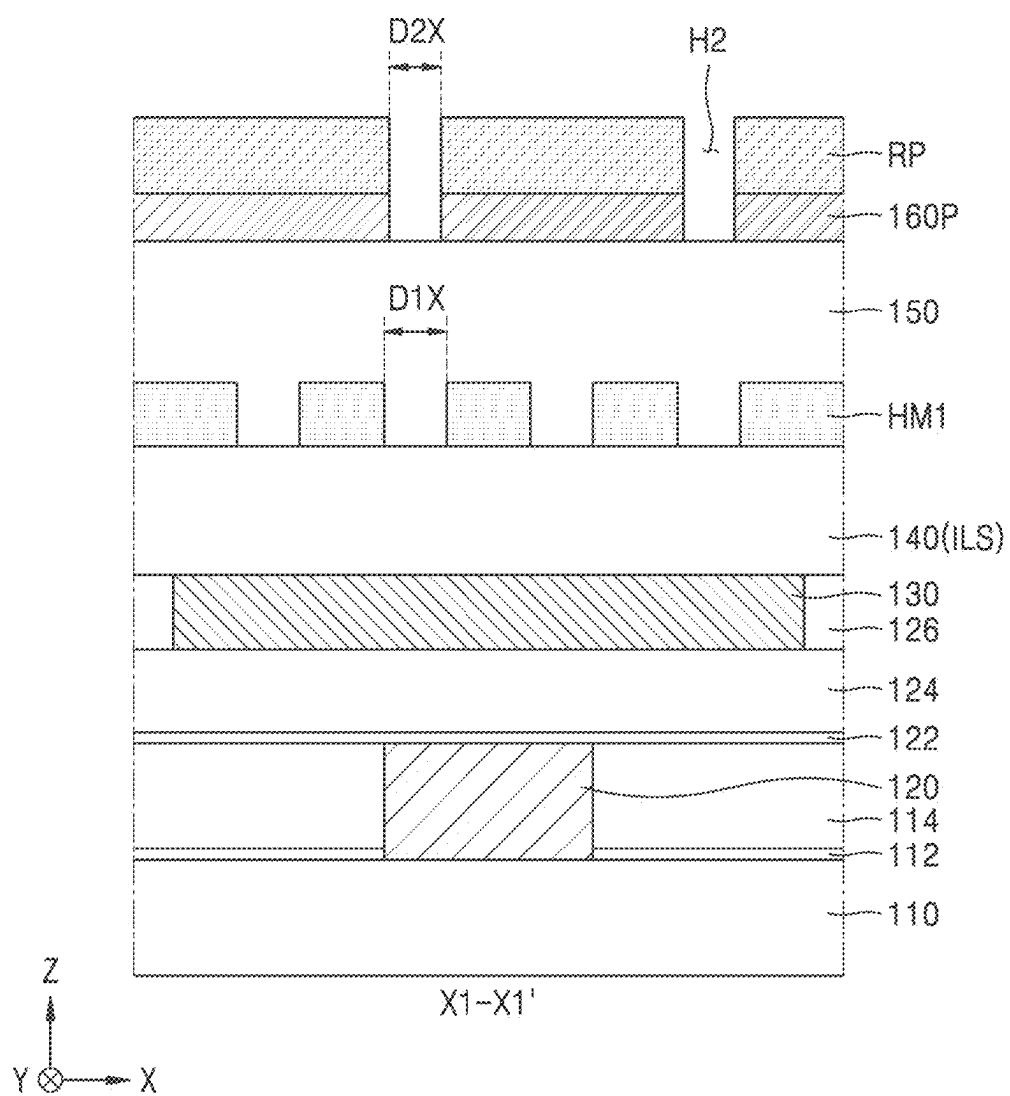


FIG. 15A

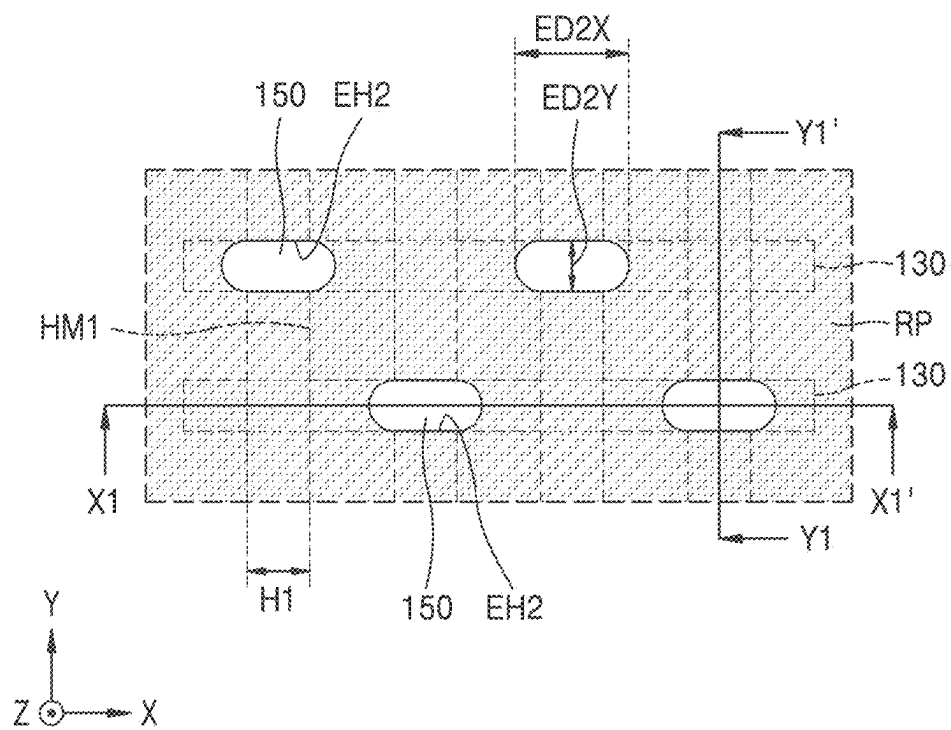


FIG. 15B

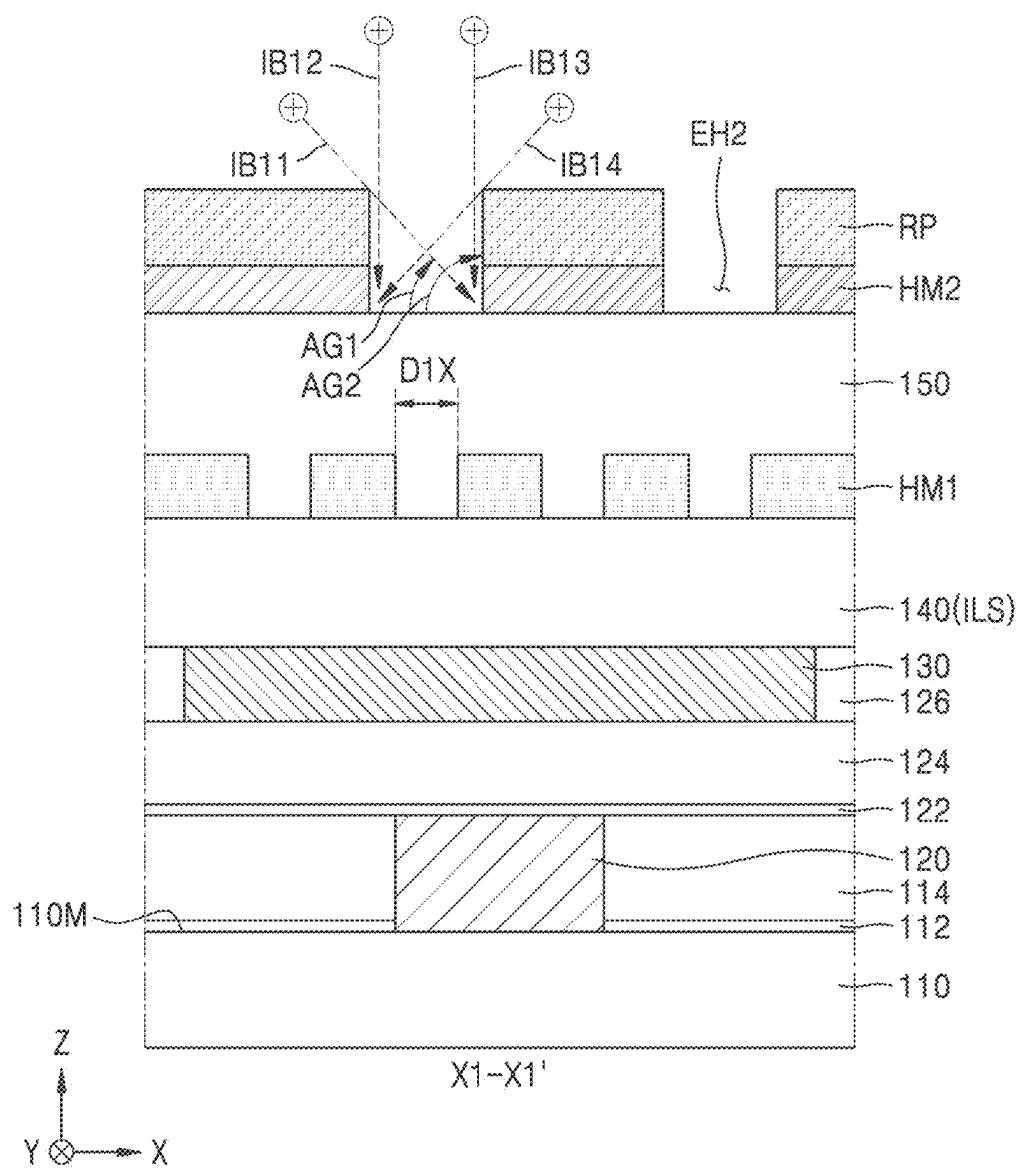


FIG. 15C

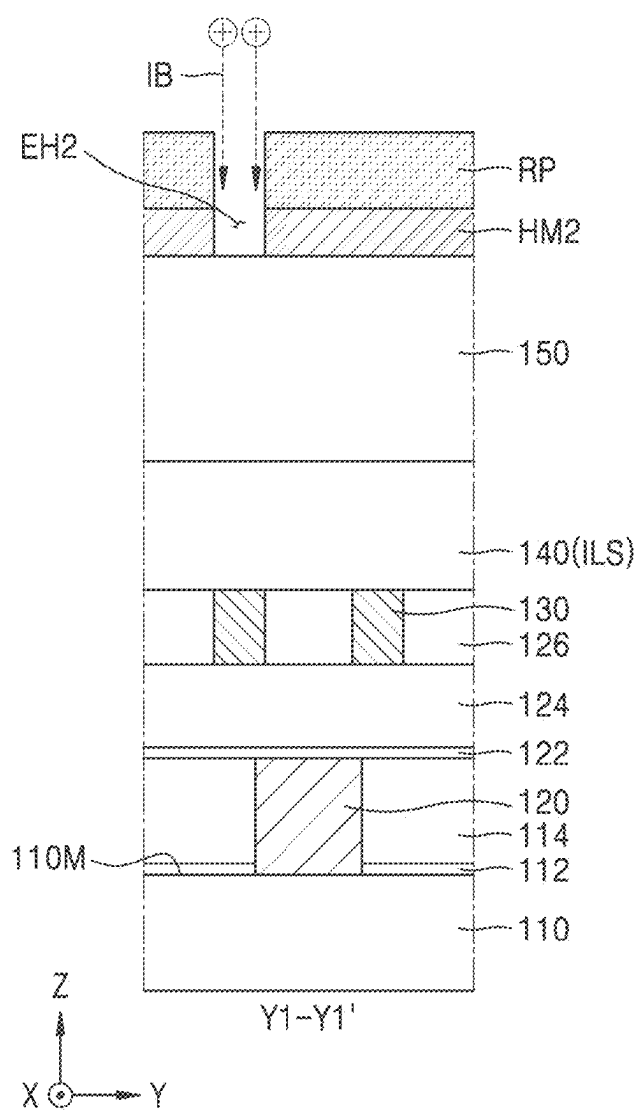


FIG. 16A

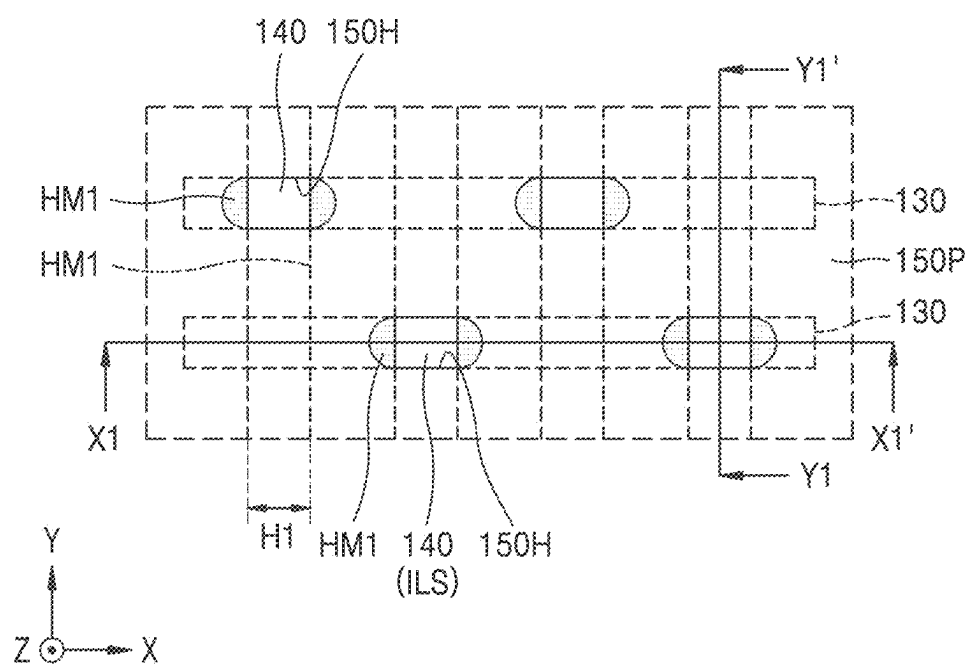


FIG. 16B

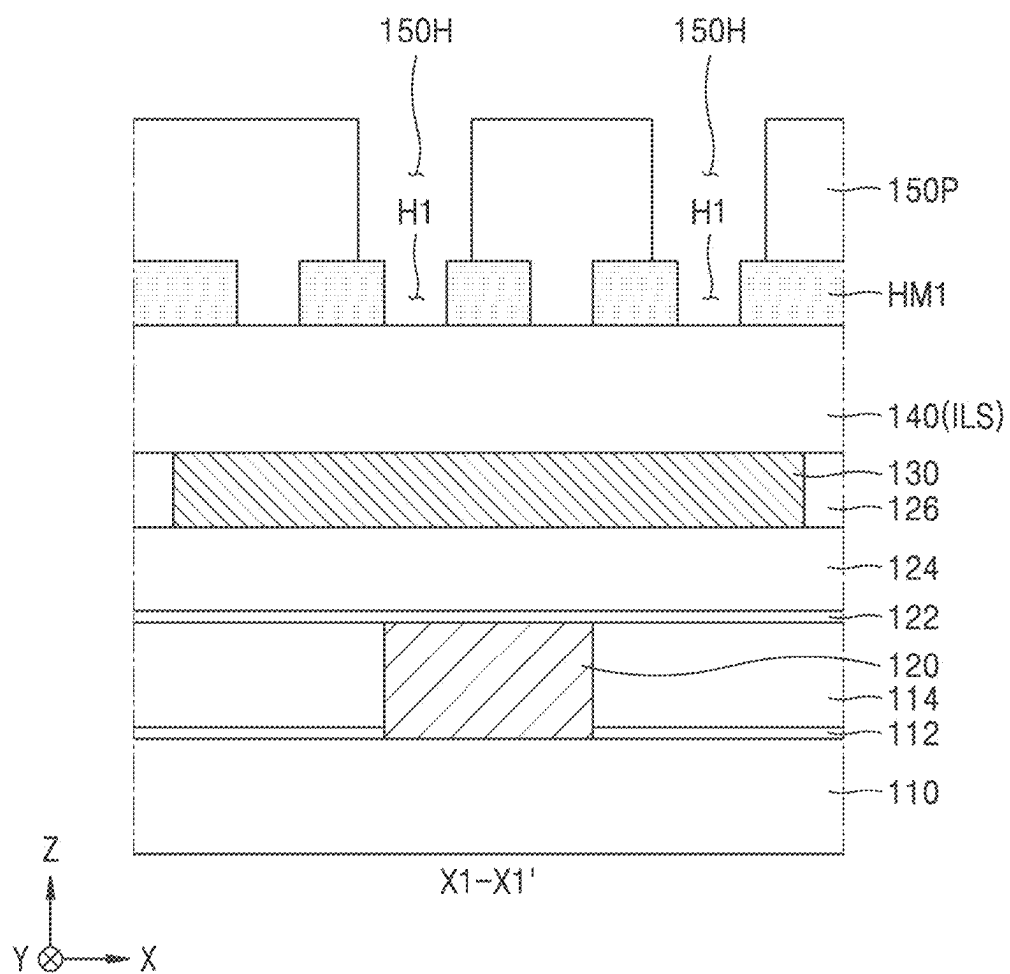


FIG. 16C

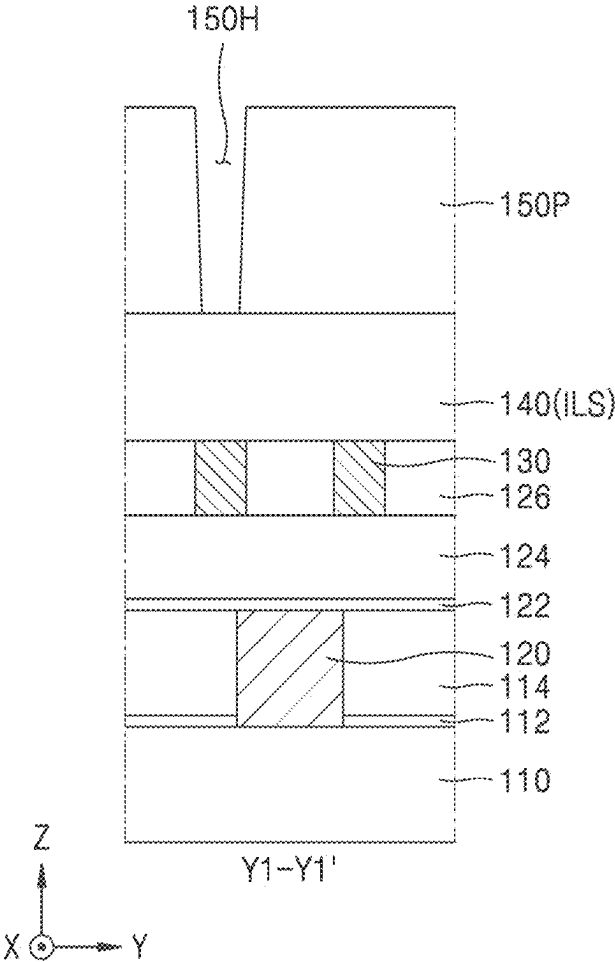


FIG. 17A

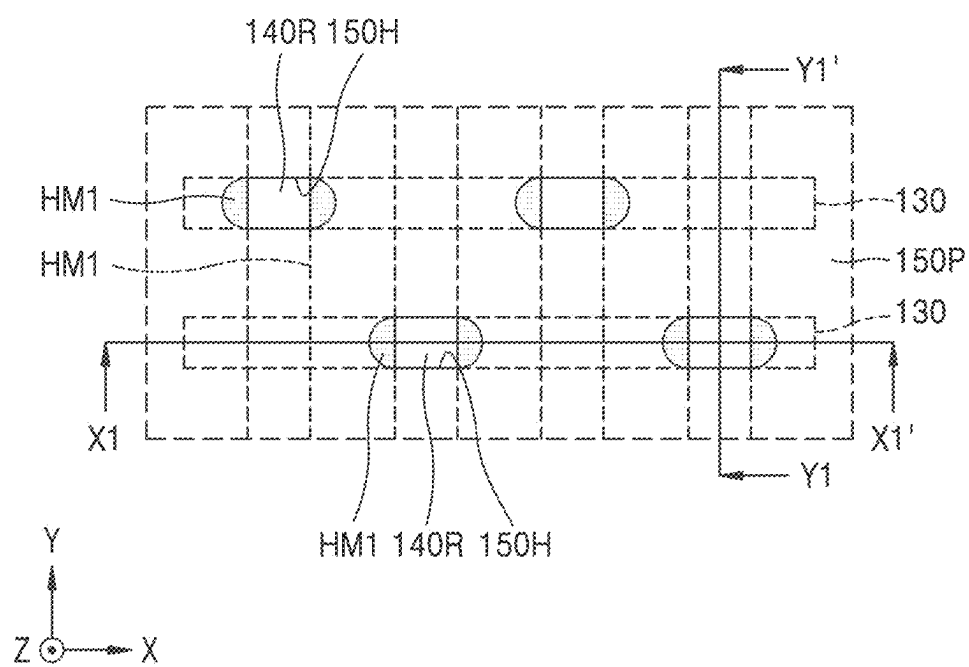




FIG. 17B

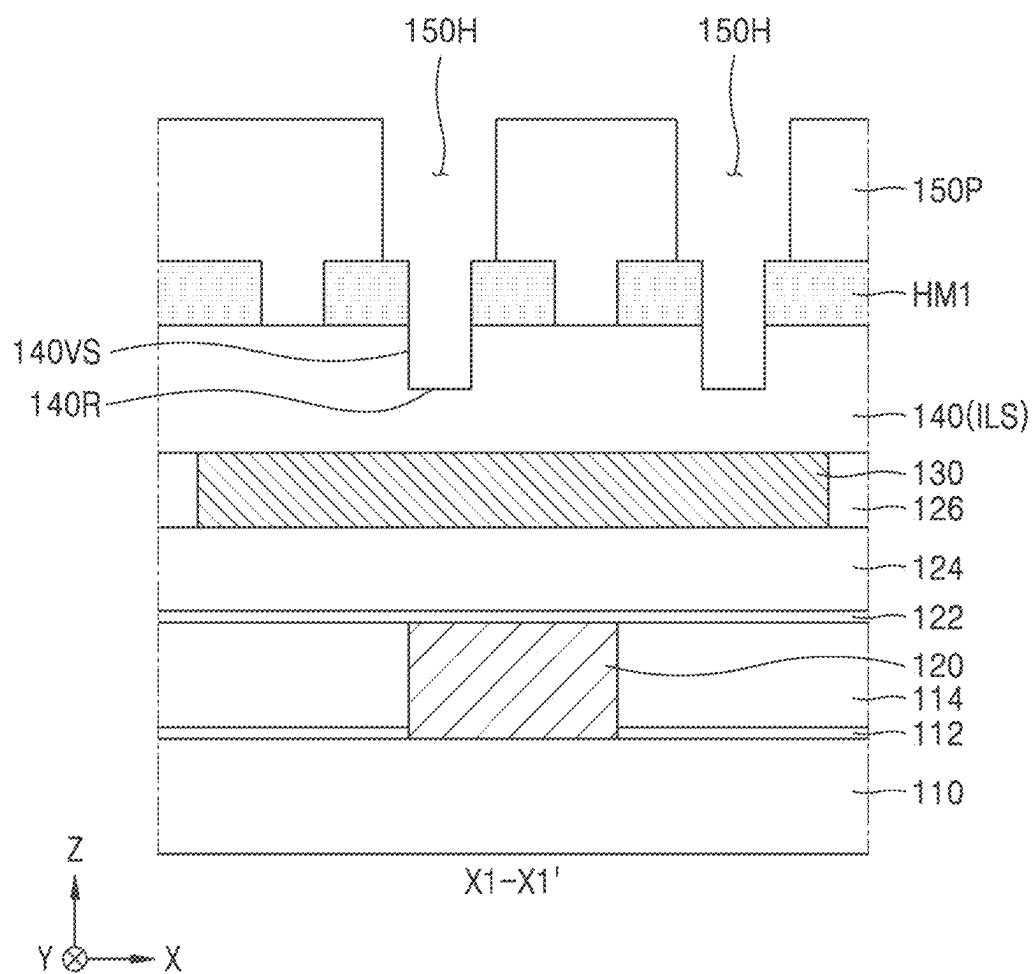


FIG. 17C

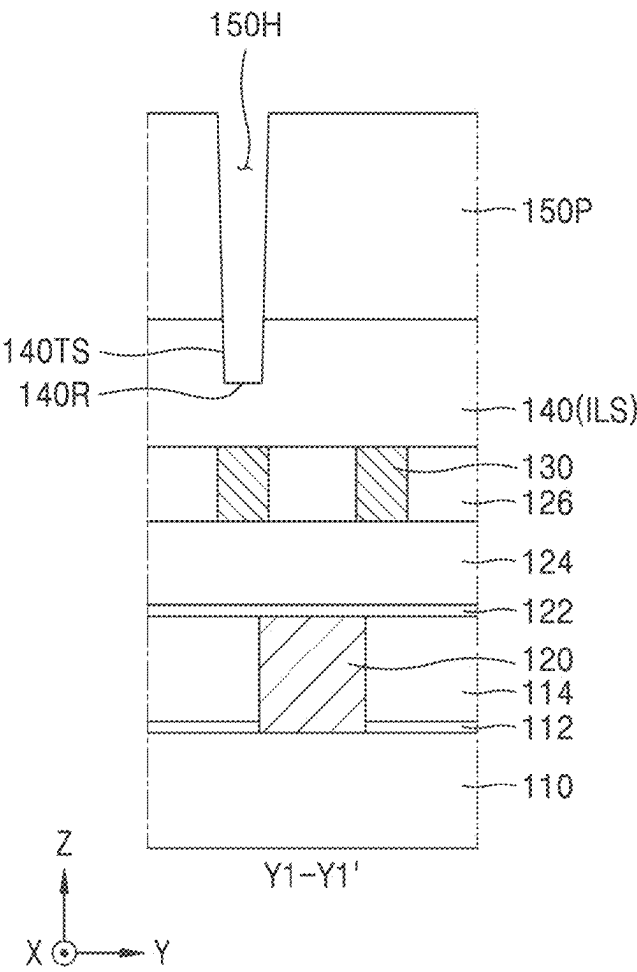


FIG. 18A

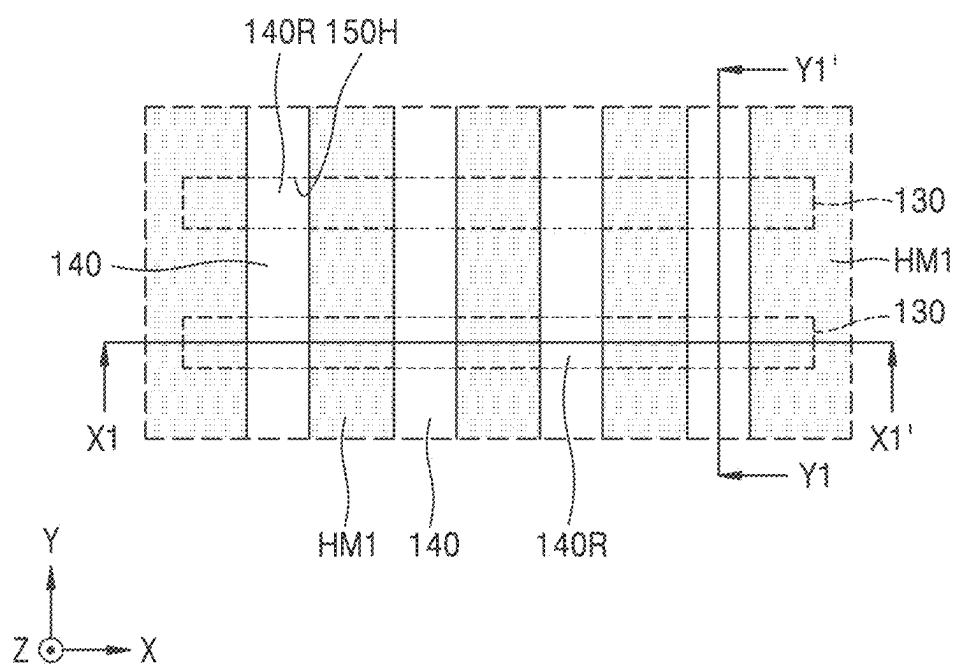


FIG. 18B

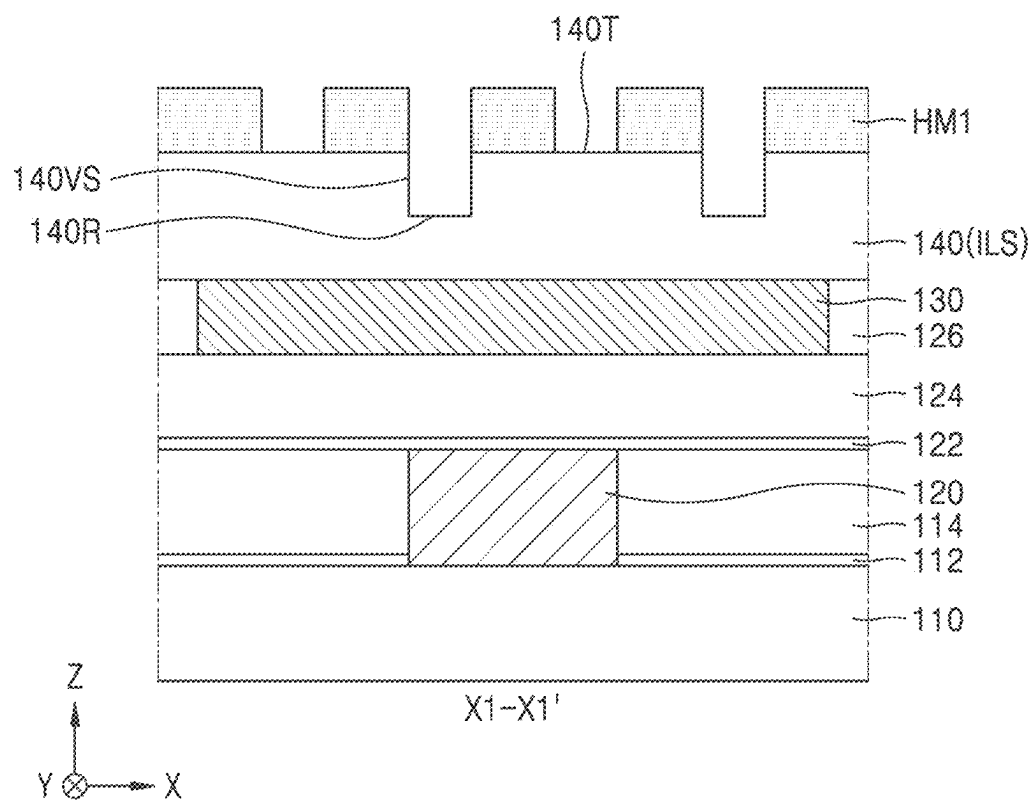


FIG. 18C

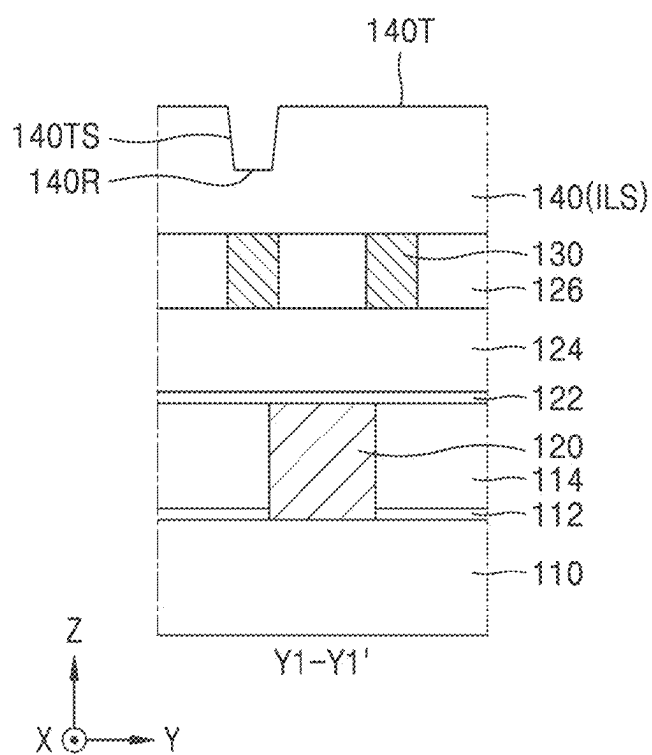


FIG. 19A

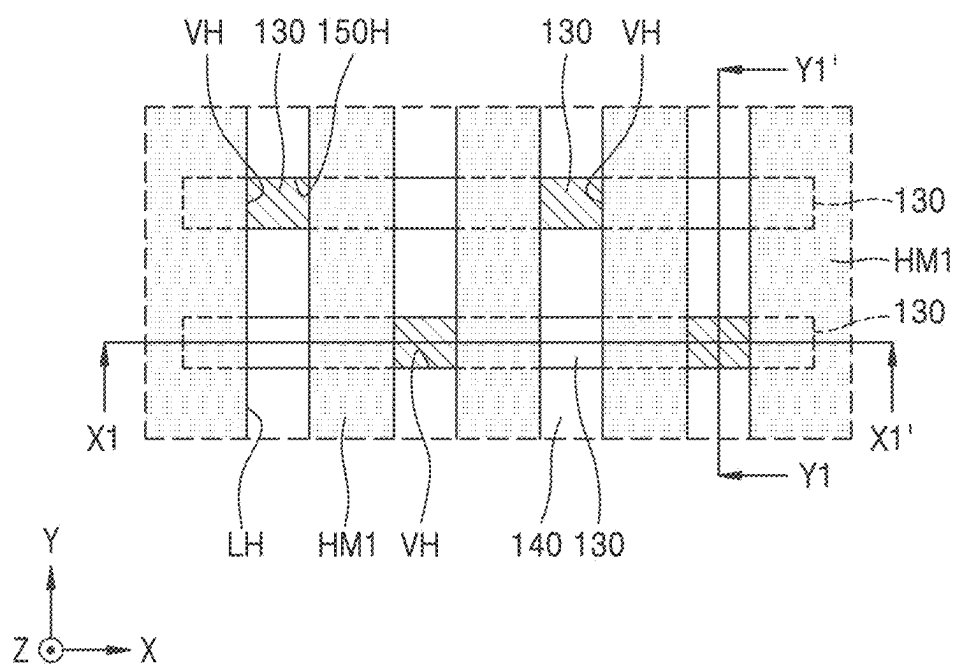


FIG. 19B

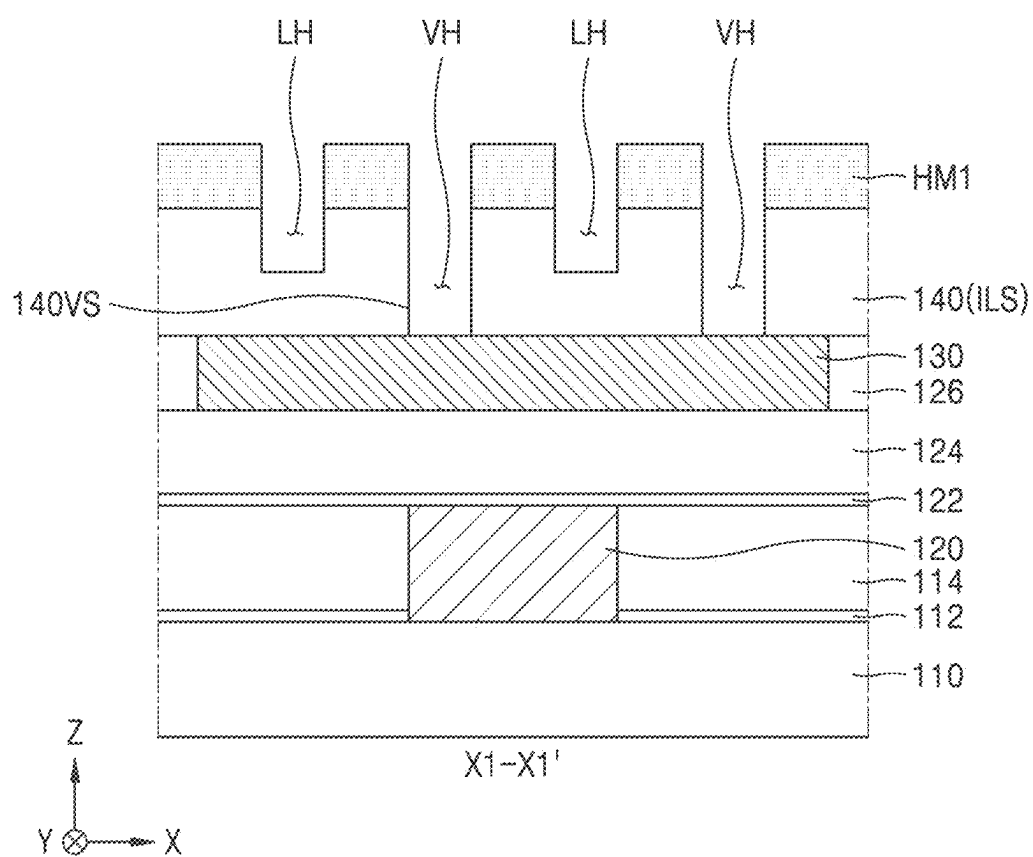


FIG. 19C

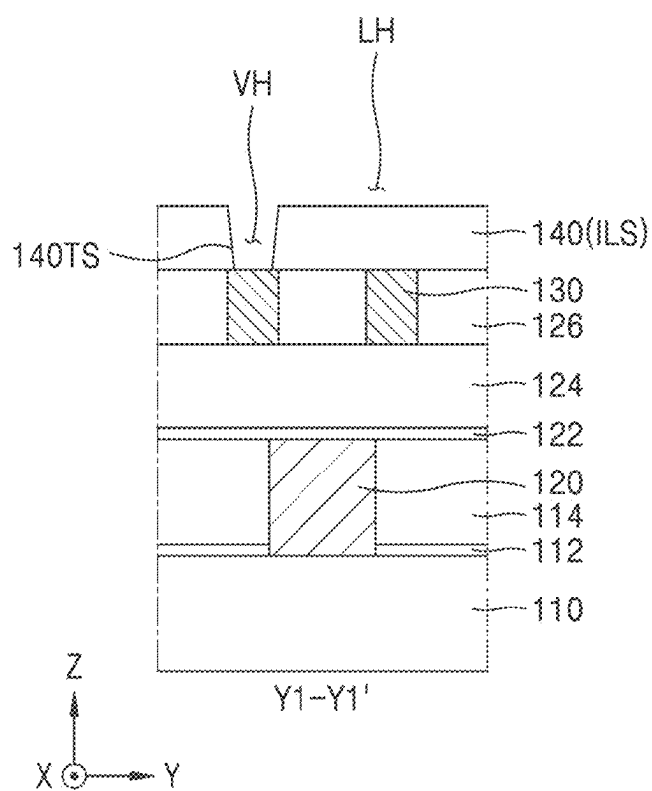




FIG. 20A

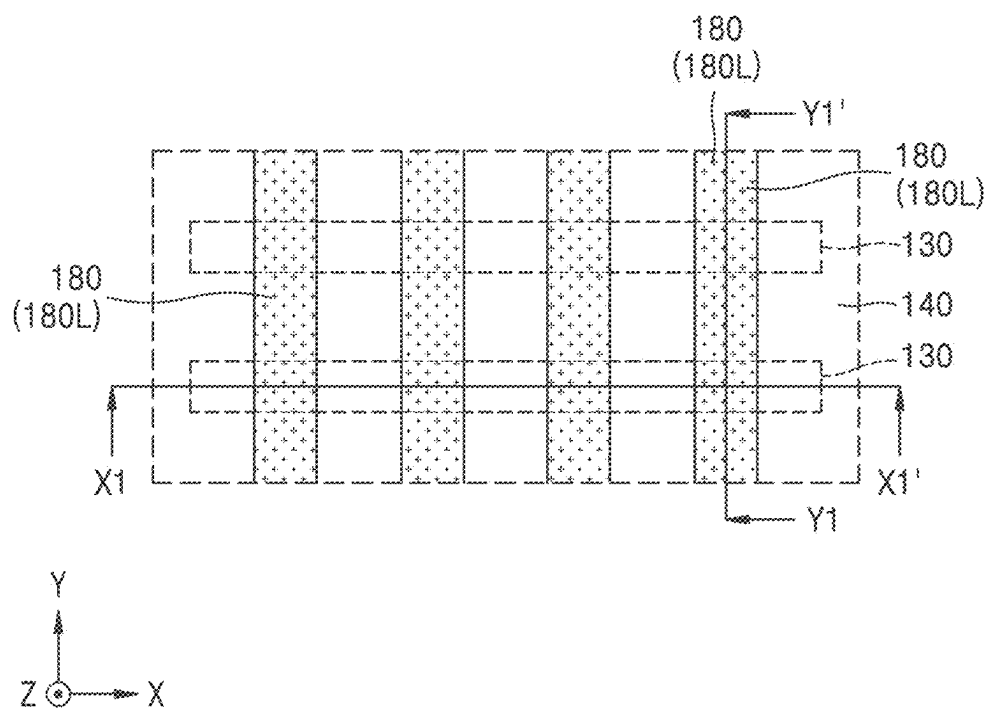


FIG. 20B

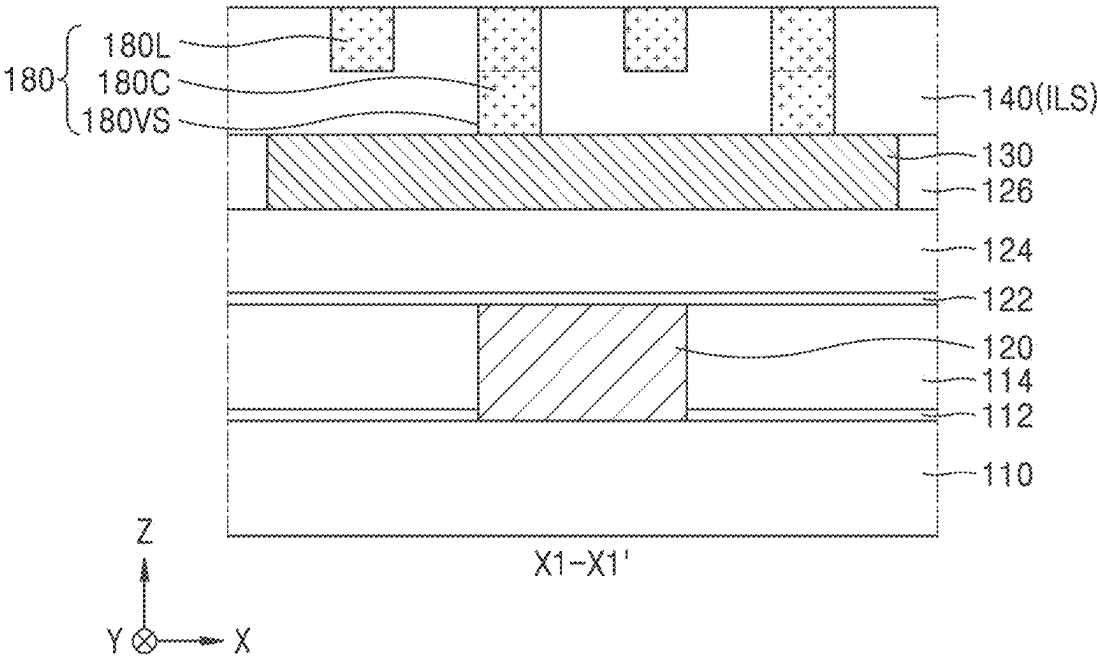


FIG. 20C

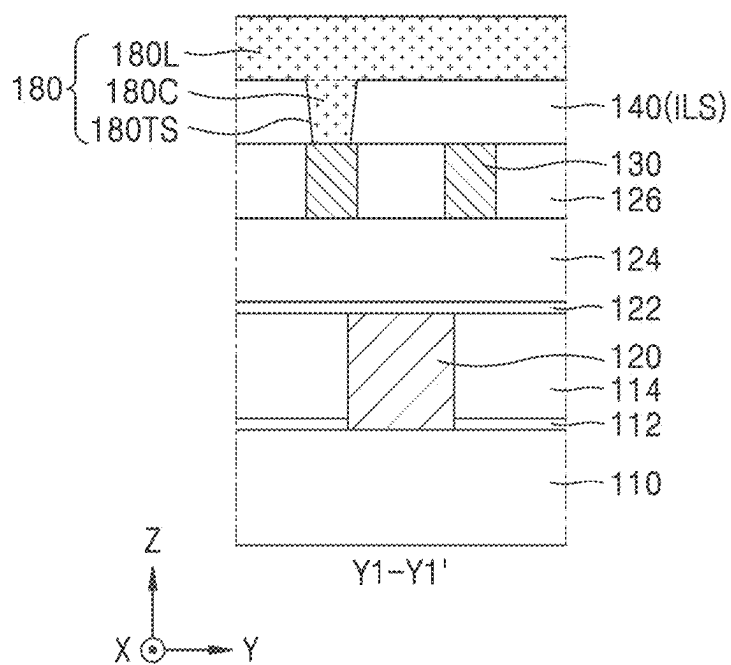


FIG. 21

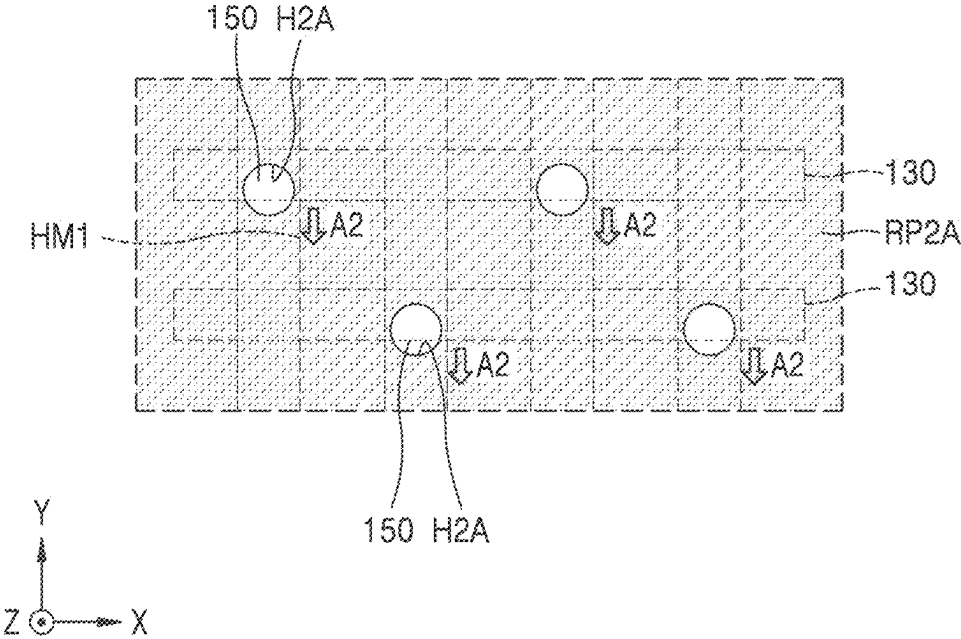
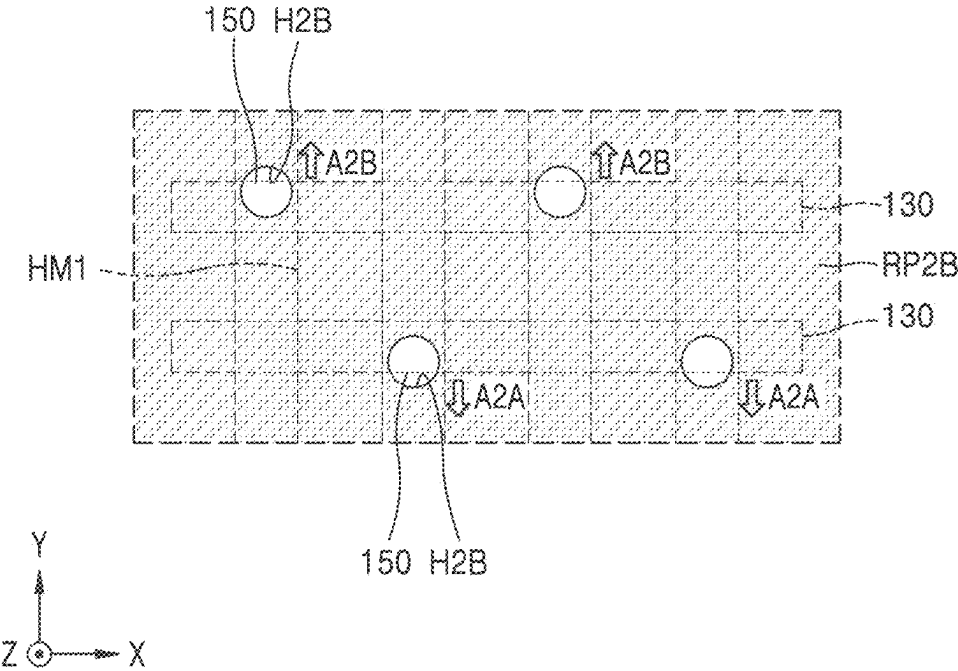


FIG. 22



## INTEGRATED CIRCUIT DEVICE AND METHOD OF MANUFACTURING THE SAME

### CROSS-REFERENCE TO RELATED APPLICATION

[0001] This application is based on and claims priority under 35 U.S.C. § 119 to Korean Patent Application Nos. 10-2024-0025306 and 10-2024-0050914, filed on Feb. 21, 2024 and Apr. 16, 2024, respectively, in the Korean Intellectual Property Office, the disclosures of which are incorporated by reference herein in their entireties.

### BACKGROUND

[0002] The inventive concepts relate to an integrated circuit (IC) devices, and more particularly, to IC devices including a metal wiring layer and methods of manufacturing the IC device.

[0003] The downscaling of IC devices has rapidly progressed due to the development of electronics technology. Thus, metal wiring layers included in the IC devices are being reduced in terms of linewidth and pitch. Accordingly, it is necessary to improve electrical reliability of metal wiring structures.

### SUMMARY

[0004] Some example embodiments of the inventive concepts provides integrated circuit (IC) devices having a structure capable of improving electrical reliability of metal wiring structures by improving the contact resistance of metal wiring structures connected to each other while reducing the possibility of short circuits between adjacent metal wiring structures.

[0005] Some example embodiments of the inventive concepts provide methods of manufacturing an IC device, which may improve electrical reliability of metal wiring structures by improving the contact resistance of metal wiring structures connected to each other while reducing the possibility of short circuits between adjacent metal wiring structures.

[0006] According to an example embodiment of the inventive concepts, an IC device includes a lower insulating film on a substrate, a lower metal wiring layer passing through the lower insulating film and extending lengthwise in a first lateral direction, an upper insulating film on the lower insulating film and the lower metal wiring layer, an upper metal wiring layer extending lengthwise in a second lateral direction on the upper insulating film, wherein the second lateral direction is perpendicular to the first lateral direction, and a conductive contact plug passing through the upper insulating film in a vertical direction, the conductive contact plug contacting each of the lower metal wiring layer and the upper metal wiring layer, wherein the conductive contact plug has a tetragonal shape in a view from above, the conductive contact plug includes a pair of first contact sidewalls, which are opposite to each other in the first lateral direction, and a pair of second contact sidewalls, which are opposite to each other in the second lateral direction, each of the pair of first contact sidewalls extends in the vertical direction from an upper line sidewall of the upper metal wiring layer to the lower metal wiring layer, and at least one of the pair of second contact sidewalls extends in a direction

inclined with respect to the vertical direction from a bottom surface of the upper metal wiring layer toward the lower metal wiring layer.

[0007] According to an example embodiment of the inventive concepts, an IC device includes a lower insulating film on a substrate, a first lower metal wiring layer and a second lower metal wiring layer each passing through the lower insulating film and extending lengthwise in a first lateral direction, the first lower metal wiring layer and the second lower metal wiring layer being apart from each other in a second lateral direction, the second lateral direction being perpendicular to the first lateral direction, an upper insulating film on each of the lower insulating film, the first lower metal wiring layer, and the second lower metal wiring layer, a first upper metal wiring layer and a second upper metal wiring layer on the upper insulating film, the first upper metal wiring layer and the second upper metal wiring layer overlapping the first lower metal wiring layer and the second lower metal wiring layer in a vertical direction and extending lengthwise in the second lateral direction, and the first upper metal wiring layer and the second upper metal wiring layer being apart from each other in the first lateral direction, a first conductive contact plug passing through the upper insulating film in the vertical direction, the first conductive contact plug contacting each of the first lower metal wiring layer and the first upper metal wiring layer, and a second conductive contact plug passing through the upper insulating film in the vertical direction, the second conductive contact plug contacting each of the second lower metal wiring layer and the second upper metal wiring layer, wherein each of the first conductive contact plug and the second conductive contact plug has a tetragonal shape in a view from above, each of the first conductive contact plug and the second conductive contact plug includes a pair of first contact sidewalls and a pair of second contact sidewalls, the pair of first contact sidewalls being opposite to each other in the first lateral direction, the pair of second contact sidewalls being opposite to each other in the second lateral direction, in each of the first conductive contact plug and the second conductive contact plug, each of the pair of first contact sidewalls extends in the vertical direction from a corresponding one of a pair of upper line sidewalls of a corresponding one of the first and second upper metal wiring layers extending in the second lateral direction to a corresponding one of the first and second lower metal wiring layers, and, in each of the first conductive contact plug and the second conductive contact plug, at least one of the pair of second contact sidewalls extends in a direction inclined with respect to the vertical direction from a bottom surface of a corresponding one of the first and second upper metal wiring layers toward the corresponding one of the first and second lower metal wiring layers.

[0008] According to an example embodiment of the inventive concepts, an IC device includes a lower structure on a substrate, a lower insulating film on the lower structure, a lower metal wiring layer passing through the lower insulating film and extending lengthwise in a first lateral direction, an upper insulating film on the lower insulating film and the lower metal wiring layer, the upper insulating film defining a line space and a via space connected to the line space, the via space extending from the line space to the lower metal wiring layer in a vertical direction, an upper metal wiring layer filling the line space, the upper metal wiring layer extending lengthwise in a second lateral direction, the sec-

ond lateral direction being perpendicular to the first lateral direction, and a conductive contact plug filling the via space and contacting each of the lower metal wiring layer and the upper metal wiring layer, wherein the upper metal wiring layer includes a portion extending from a top surface of the upper insulating film to a top surface of the conductive contact plug in the vertical direction, the conductive contact plug has a tetragonal shape in a view from above, the conductive contact plug includes a pair of first contact sidewalls and a pair of second contact sidewalls, the pair of first contact sidewalls being opposite to each other in the first lateral direction and facing the upper insulating film, the pair of second contact sidewalls being opposite to each other in the second lateral direction and facing the upper insulating film, each of the pair of first contact sidewalls extends in the vertical direction from a corresponding one upper line sidewall adjacent thereto, from among a pair of upper line sidewalls included in the upper metal wiring layer, to the lower metal wiring layer, the pair of upper line sidewalls being opposite to each other in the first lateral direction, and at least one of the pair of second contact sidewalls extends in a direction inclined with respect to the vertical direction from a bottom surface of the upper metal wiring layer toward the lower metal wiring layer.

**[0009]** According to an example embodiment of the inventive concepts, a method of manufacturing an IC device includes forming a lower insulating film and a lower metal wiring layer on a substrate, the lower metal wiring layer passing through the lower insulating film and extending lengthwise in a first lateral direction on the substrate. An upper metal wiring structure is formed on the lower insulating film and the lower metal wiring layer. The upper metal wiring structure includes an upper metal wiring layer and a conductive contact plug, the upper metal wiring layer extending lengthwise in a second lateral direction on the lower insulating film and the lower metal wiring layer, the conductive contact plug being integrally connected to the upper metal wiring layer and contacting the lower metal wiring layer, wherein the second lateral direction is perpendicular to the first lateral direction. The conductive contact plug has a tetragonal shape in a view from above, the conductive contact plug includes a pair of first contact sidewalls and a pair of second contact sidewalls, the pair of first contact sidewalls being opposite to each other in the first lateral direction, and the pair of second contact sidewalls being opposite to each other in the second lateral direction, each of the pair of first contact sidewalls extends in a vertical direction from a corresponding one of a pair of upper line sidewalls of the upper metal wiring layer to the lower metal wiring layer, the pair of upper line sidewalls of the upper metal wiring layer being opposite to each other in the first lateral direction, and at least one of the pair of second contact sidewalls extends in a direction inclined with respect to the vertical direction from a bottom surface of the upper metal wiring layer toward the lower metal wiring layer.

**[0010]** According to an example embodiment of the inventive concepts, a method of manufacturing an IC device includes forming a lower insulating film, a first lower metal wiring layer, and a second lower metal wiring layer on a substrate, the first lower metal wiring layer and the second lower metal wiring layer passing through the lower insulating film and extending lengthwise in a first lateral direction on the substrate, and the first lower metal wiring layer and the second lower metal wiring layer being apart from each

other in a second lateral direction, the second lateral direction being perpendicular to the first lateral direction, forming an upper insulating film on the lower insulating film, the first lower metal wiring layer, and the second lower metal wiring layer; and forming a plurality of upper metal wiring structures in the upper insulating film and on the lower insulating film, the first lower metal wiring layer, and the second lower metal wiring layer. The plurality of upper metal wiring structures include a first upper metal wiring layer and a second upper metal wiring layer overlapping the first lower metal wiring layer and the second lower metal wiring layer in a vertical direction, the first upper metal wiring layer and the second upper metal wiring layer extending lengthwise in the second lateral direction and being apart from each other in the first lateral direction, a first conductive contact plug contacting each of the first lower metal wiring layer and the first upper metal wiring layer; and a second conductive contact plug contacting each of the second lower metal wiring layer and the second upper metal wiring layer. Each of the first conductive contact plug and the second conductive contact plug has a tetragonal shape in a view from above, each of the first conductive contact plug and the second conductive contact plug includes a pair of first contact sidewalls and a pair of second contact sidewalls, the pair of first contact sidewalls being opposite to each other in the first lateral direction and facing the upper insulating film, the pair of second contact sidewalls being opposite to each other in the second lateral direction and facing the upper insulating film. In each of the first conductive contact plug and the second conductive contact plug, each of the pair of first contact sidewalls extends in the vertical direction, and at least one of the pair of second contact sidewalls extends in a direction inclined with respect to the vertical direction.

**[0011]** According to an example embodiment of the inventive concepts, a method of manufacturing an IC device includes forming a lower insulating film, a first lower metal wiring layer, and a second lower metal wiring layer on a substrate, the first lower metal wiring layer and the second lower metal wiring layer passing through the lower insulating film and extending lengthwise in a first lateral direction on the substrate, and the first lower metal wiring layer and the second lower metal wiring layer being apart from each other in a second lateral direction that is perpendicular to the first lateral direction, forming a plurality of upper metal wiring structures on the lower insulating film, the first lower metal wiring layer, and the second lower metal wiring layer. The forming of the plurality of upper metal wiring structures includes forming an upper insulating film including a line space and a via space on the lower insulating film and the lower metal wiring layer, the line space being apart from each of the lower insulating film and the lower metal wiring layer in the vertical direction, the via space being connected to the line space and exposing the lower metal wiring layer, and forming a metal-containing conductive layer to fill the via space and the line space. The forming of the upper insulating film including the line space and the via space includes forming an upper insulating film having a planarized top surface on the lower insulating film and the lower metal wiring layer, forming, on the upper insulating film having the planarized top surface, a first hard mask pattern including a first opening, the first opening exposing a top surface of the upper insulating film, forming a planarized hard mask layer to cover the upper insulating film and the first hard mask pattern, forming, on the planarized hard

mask layer, an inorganic hard mask pattern having a second opening, the second opening overlapping the first opening in the vertical direction, and forming a second hard mask pattern having an extended second opening from the inorganic hard mask pattern having the second opening by selectively increasing only a first width of the second opening in the first lateral direction, from among the first width and a second width of the second opening in the second lateral direction, and wherein the formation of the second hard mask pattern having the extended second opening includes performing an ion beam etch process in the first lateral direction while varying an ion beam incidence direction within a range between 50° and 90° with respect to a straight line parallel to a main surface of the substrate and performing an ion beam etch process in the second lateral direction while ion beams are incident in a direction perpendicular to the main surface of the substrate.

#### BRIEF DESCRIPTION OF THE DRAWINGS

[0012] Example embodiments will be more clearly understood from the following detailed description taken in conjunction with the accompanying drawings in which:

[0013] FIG. 1A is a plan layout diagram of an integrated circuit (IC) device according to an example embodiment;

[0014] FIG. 1B is a cross-sectional view taken along line X1-X1' of FIG. 1A;

[0015] FIG. 1C is a cross-sectional view taken along line Y1-Y1' of FIG. 1A;

[0016] FIG. 2 is a partial perspective view of some components of the IC device shown in FIGS. 1A, 1B, and 1C;

[0017] FIG. 3A is a plan layout diagram of an IC device according to an example embodiment;

[0018] FIG. 3B is a cross-sectional view taken along line X1-X1' of FIG. 3A;

[0019] FIG. 3C is a cross-sectional view taken along line Y1-Y1' of FIG. 3A;

[0020] FIG. 4 is a partial perspective view of some components of the IC device shown in FIGS. 3A, 3B, and 3C;

[0021] FIG. 5A is a plan layout diagram of an IC device according to an example embodiment;

[0022] FIG. 5B is a cross-sectional view taken along lines Y1-Y1' and Y2-Y2' of FIG. 5A;

[0023] FIGS. 6A and 6B are cross-sectional views of an IC device according to an example embodiment;

[0024] FIG. 7 is a plan layout diagram of an IC device according to an example embodiment;

[0025] FIG. 8 is a cross-sectional view taken along line X1-X1' of FIG. 7;

[0026] FIG. 9 is a cross-sectional view taken along line Y1-Y1' of FIG. 7;

[0027] FIG. 10 is a cross-sectional view of an IC device according to an example embodiment;

[0028] FIGS. 11A, 12A, 13A, 14A, 15A, 16A, 17A, 18A, 19A, and 20A are plan views of process sequences of methods of manufacturing IC devices, according to an example embodiment, FIGS. 11B, 12B, 13B, 14B, 15B, 16B, 17B, 18B, 19B, and 20B are cross-sectional views taken along lines X1-X1' of FIGS. 11A, 12A, 13A, 14A, 15A, 16A, 17A, 18A, 19A, and 20A, respectively, and FIGS. 15C, 16C, 17C, 18C, 19C, and 20C are cross-sectional views taken along lines Y1-Y1' of FIGS. 15A, 16A, 17A, 18A, 19A, and 20A, respectively;

[0029] FIG. 21 is a plan view illustrating a method of manufacturing an IC device, according to an example embodiment; and

[0030] FIG. 22 is a plan view illustrating a method of manufacturing an IC device, according to an example embodiment.

#### DETAILED DESCRIPTION

[0031] Hereinafter, some example embodiments will be described in detail with reference to the accompanying drawings. The same reference numerals are used to denote the same elements in the drawings, and repeated descriptions thereof are omitted.

[0032] Terms such as “first” and “second” are used herein merely to describe a variety of constituent elements, but the constituent elements are not limited by the terms. Such terms are used only for the purpose of distinguishing one constituent element from another constituent element. For example, without departing from the right scope of various example embodiments described below, a first constituent element may be referred to as a second constituent element, and vice versa. When constituent elements are separately referred to as a first constituent element and a second constituent element in the following detailed description and claims, they are not the same constituent element. While the term “same,” “equal” or “identical” is used in description of example embodiments, it should be understood that some imprecisions may exist. Thus, when one element is referred to as being the same as another element, it should be understood that an element or a value is the same as another element within a desired manufacturing or operational tolerance range (e.g.,  $\pm 10\%$ ).

[0033] When the term “about,” “substantially” or “approximately” is used in this specification in connection with a numerical value, it is intended that the associated numerical value includes a manufacturing or operational tolerance (e.g.,  $\pm 10\%$ ) around the stated numerical value. Moreover, when the word “about,” “substantially” or “approximately” is used in connection with geometric shapes, it is intended that precision of the geometric shape is not required but that latitude for the shape is within the scope of the disclosure. Further, regardless of whether numerical values or shapes are modified as “about” or “substantially,” it will be understood that these values and shapes should be construed as including a manufacturing or operational tolerance (e.g.,  $\pm 10\%$ ) around the stated numerical values or shapes.

[0034] As used herein, expressions such as “at least one of,” when preceding a list of elements, modify the entire list of elements and do not modify the individual elements of the list. Thus, for example, both “at least one of A, B, or C” and “at least one of A, B, and C” mean either A, B, C or any combination thereof. Likewise, A and/or B means A, B, or A and B.

[0035] FIG. 1A is a plan layout diagram of an IC device 100 according to an example embodiment. FIG. 1B is a cross-sectional view taken along line X1-X1' of FIG. 1A. FIG. 1C is a cross-sectional view taken along line Y1-Y1' of FIG. 1A. FIG. 2 is a partial perspective view of some components of the IC device 100.

[0036] Referring to FIGS. 1A, 1B, 1C, and 2, the IC device 100 may include a lower structure on a substrate 110. The lower structure may include a first lower etch stop film 112, a first interlayer insulating film 114, a second lower etch



stop film **122**, and a second interlayer insulating film **124**, which are sequentially on a main surface **110M** of the substrate **110** in a vertical direction (Z direction), and a conductive structure **120** passing through the first interlayer insulating film **114** and the first lower etch stop film **112** in the vertical direction (Z direction).

[0037] The substrate **110** may include a semiconductor, such as silicon (Si) or germanium (Ge), or a compound semiconductor, such as silicon germanium (SiGe), silicon carbide (SiC), gallium arsenide (GaAs), indium arsenide (InAs), or indium phosphide (InP). The substrate **110** may include a conductive region (not shown). The conductive region may include a doped well, a doped structure, or a conductive layer. The substrate **110** may include circuit elements (not shown), such as a gate structure, an impurity region, and a contact plug.

[0038] Each of the first interlayer insulating film **114** and the second interlayer insulating film **124** may include a silicon oxide film. For example, each of the first interlayer insulating film **114** and the second interlayer insulating film **124** may include a silicon-oxide-based material, such as plasma enhanced oxide (PEOX), tetraethyl orthosilicate (TEOS), boro TEOS (BTEOS), phosphorous TEOS (PTEOS), boro phospho TESO (BPTEOS), boro silicate glass (BSG), phospho silicate glass (PSG), and boro PSG (BPSG). In other example embodiments, each of the first interlayer insulating film **114** and the second interlayer insulating film **124** may have a low-k dielectric film (e.g., a SiOC film or a SiCOH film) having a low dielectric constant K of about 2.2 to about 3.0.

[0039] Each of the first lower etch stop film **112** and the second lower etch stop film **122** may include a material having a different etch selectivity from a constituent material of each of the first interlayer insulating film **114** and the second interlayer insulating film **124**. For example, each of the first lower etch stop film **112** and the second lower etch stop film **122** may include a silicon nitride film, a carbon-doped silicon nitride film, or a carbon-doped silicon oxynitride film. In some example embodiments, each of the first lower etch stop film **112** and the second lower etch stop film **122** may include an insulating metal oxide film, an insulating metal nitride film, or a combination thereof. For example, the first lower etch stop film **112** and the second lower etch stop film **122** may include an aluminum oxide film (AlO film), an aluminum nitride film (AlN film), or a combination thereof.

[0040] In some example embodiments, the conductive structure **120** may be a wiring layer including a metal film and a conductive barrier film surrounding the metal film. In the conductive structure **120**, the metal film may include copper (Cu), tungsten (W), molybdenum (Mo), ruthenium (Ru), cobalt (Co), aluminum (Al), or a combination thereof, and the conductive barrier film may include a titanium nitride (TiN) film, a tantalum nitride (TaN) film, a cobalt (Co) film, or a combination thereof, without being limited thereto. In some example embodiments, the conductive structure **120** may be electrically connected to the conductive region formed in the substrate **110**. In other example embodiments, the conductive structure **120** may be connected to a source/drain region (not shown) or a gate electrode (not shown) of a transistor formed in the substrate **110**.

[0041] A lower insulating film **126** may be on the second interlayer insulating film **124**, and a plurality of lower metal

wiring layers **130** may pass through the lower insulating film **126** in the vertical direction (Z direction). The plurality of lower metal wiring layers **130** may extend lengthwise in a first lateral direction (X direction) and be apart from each other in a second lateral direction (Y direction), which is perpendicular to the first lateral direction (X direction). The plurality of lower metal wiring layers **130** may extend parallel to each other.

[0042] An upper insulating film **140** may be on the lower insulating film **126** and the plurality of lower metal wiring layers **130**. As used herein, the upper insulating film **140** may be referred to as an upper insulating structure ILS. Constituent materials of the lower insulating film **126** and the upper insulating film **140** are the same as or substantially similar to those of the first interlayer insulating film **114** and the second interlayer insulating film **124**, which have been described above.

[0043] A plurality of upper metal wiring structures **180** may be on the upper insulating film **140**. Each of the plurality of upper metal wiring structures **180** may include an upper metal wiring layer **180L** and a conductive contact plug **180C** integrally connected to the upper metal wiring layer **180L**.

[0044] The upper insulating film **140** may have a shape defining a line space LH and a via space VH connected to the line space LH. The via space VH may extend from the line space LH to the lower metal wiring layer **130** in the vertical direction (Z direction). The line space LH may extend lengthwise in the second lateral direction (Y direction). Respective sectional shapes of the line space LH and the via space VH defined by the upper insulating film **140** in each of the first lateral direction (X direction) and the second lateral direction (Y direction) are illustrated more clearly in FIGS. 19B and 19C. In each of the plurality of upper metal wiring structures **180**, the upper metal wiring layer **180L** may fill the line space LH defined by the upper insulating film **140**, and the conductive contact plug **180C** may fill the via space VH defined by the upper insulating film **140**. The upper metal wiring layer **180L** may include a portion extending from a top surface **140T** of the upper insulating film **140** to a top surface of the conductive contact plug **180C** in the vertical direction (Z direction).

[0045] In each of the plurality of upper metal wiring structures **180**, the upper metal wiring layer **180L** may overlap at least one lower metal wiring layer **130** selected from the plurality of lower metal wiring layers **130** in a vertical direction. In the plurality of upper metal wiring structures **180**, each of a plurality of upper metal wiring layers **180L** may extend lengthwise in the second lateral direction (Y direction) and be apart from each other in the first lateral direction (X direction). The plurality of upper metal wiring layers **180L** may extend parallel to each other. Each of the plurality of upper metal wiring layers **180L** may be on the upper insulating film **140** and overlap a plurality of lower metal wiring layers **130** in the vertical direction (Z direction).

[0046] The conductive contact plug **180C** may be at an intersection between a selected one of the plurality of lower metal wiring layers **130** and a selected one of the plurality of upper metal wiring structures **180**. In FIG. 1A, a plurality of conductive contact plugs **180C** included in the plurality of upper metal wiring structures **180** are illustrated with dashed lines. As shown in FIG. 1A, each of the plurality of

conductive contact plugs **180C** may have a tetragonal shape in a view from above (on an X-Y plane).

[0047] Each of the plurality of lower metal wiring layers **130** and the plurality of upper metal wiring layers **180L** may include a metal film, a conductive metal nitride film, or a combination thereof. In some example embodiments, at least one of the plurality of lower metal wiring layers **130** or the plurality of upper metal wiring layers **180L** may include a metal plug and a conductive barrier film surrounding a sidewall and a bottom surface of the metal plug. The metal plug may include copper (Cu), tungsten (W), molybdenum (Mo), ruthenium (Ru), cobalt (Co), aluminum (Al), or a combination thereof. For example, the metal plug may include copper (Cu). The conductive barrier film may include a TiN film, a TaN film, a Co film, or a combination thereof. For example, when the metal plug includes Cu, the conductive barrier film may have a multilayered structure including a TaN film and a Co film, without being limited thereto.

[0048] Each of the plurality of conductive contact plugs **180C** included in the plurality of upper metal wiring structures **180** may pass through the upper insulating film **140** in the vertical direction (Z direction) and contact a selected one of the plurality of lower metal wiring layers **130**. Each of the plurality of conductive contact plugs **180C** may extend in the vertical direction (Z direction) between a selected one of the plurality of upper metal wiring layers **180L** and a selected one of the plurality of lower metal wiring layers **130** and contact each of the selected upper metal wiring layer **180L** and the selected lower metal wiring layer **130**.

[0049] For example, as shown in FIG. 1A, the plurality of conductive contact plugs **180C** may include a first conductive contact plug **180CA** and a second conductive contact plug **180CB**. As shown in FIGS. 1A, 1B, and 1C, the first conductive contact plug **180CA** may extend in the vertical direction (Z direction) between a first lower metal wiring layer **130A**, which is a selected one of the plurality of lower metal wiring layers **130**, and a first upper metal wiring layer **180LA**, which is a selected one of the plurality of upper metal wiring layers **180L**, and contact each of the first lower metal wiring layer **130A** and the first upper metal wiring layer **180LA**. The second conductive contact plug **180CB** may extend in the vertical direction (Z direction) between a second lower metal wiring layer **130B**, which is a selected one of the plurality of lower metal wiring layers **130**, and a second upper metal wiring layer **180LB**, which is a selected one of the plurality of upper metal wiring layers **180L**, and contact each of the second lower metal wiring layer **130B** and the second upper metal wiring layer **180LB**.

[0050] As shown in FIGS. 1B, 1C, and 2, each of the plurality of conductive contact plugs **180C** may include a pair of first contact sidewalls **180VS** and a pair of second contact sidewalls **180TS**. The pair of first contact sidewalls **180VS** may be opposite to each other in the first lateral direction (X direction) and each face the upper insulating film **140**. The pair of second contact sidewalls **180TS** may be opposite to each other in the second lateral direction (Y direction) and each face the upper insulating film **140**.

[0051] Each of the plurality of upper metal wiring layers **180L** may include a pair of upper line sidewalls (refer to **180LS** in FIGS. 1B and 2), which are opposite to each other in the first lateral direction (X direction). The pair of upper line sidewalls **180LS** may extend in the vertical direction (Z

direction), which is that is perpendicular to the main surface **110M** of the substrate **110**, on a plane (Y-Z plane).

[0052] In each of the plurality of conductive contact plugs **180C**, each of the pair of first contact sidewalls **180VS** may extend in the vertical direction (Z direction), which is perpendicular to the main surface **110M** of the substrate **110**, on the plane (Y-Z plane). Each of the pair of first contact sidewalls **180VS** may extend in the vertical direction (Z direction) from one upper line sidewall **180LS** adjacent thereto, from among the pair of upper line sidewalls (refer to **180LS** in FIGS. 1B and 2) included in a corresponding one of the plurality of upper metal wiring layers **180L**, to a corresponding one of the plurality of lower metal wiring layers **130**. As used herein, it will be understood that when a constituent element is referred to as corresponding to another constituent element, it can be connected to the other constituent element.

[0053] In each of the plurality of conductive contact plugs **180C**, at least one of the pair of second contact sidewalls **180TS** may extend in a direction inclined with respect to the vertical direction (Z direction) from a bottom surface of a corresponding one of the plurality of upper metal wiring layers **180L** toward a corresponding one of the plurality of lower metal wiring layers **130**. For example, as shown in FIGS. 1C and 2, each of the pair of second contact sidewalls **180TS** may have an inclined surface that gets close to a vertical central axis of the conductive contact plug **180C** toward (e.g., as it gets close to) a corresponding one of the lower metal wiring layers **130**.

[0054] As shown in FIG. 1B, in the plurality of upper metal wiring structures **180**, the upper metal wiring layer **180L** and the conductive contact plug **180C**, which are connected to each other, may have a same width **WX** in the first lateral direction (X direction), and the width **WX** of each of the upper metal wiring layer **180L** and the conductive contact plug **180C** in the first lateral direction (X direction) may be constant in the vertical direction (Z direction). In some example embodiments, a width of each of the plurality of conductive contact plugs **180C** in the second lateral direction (Y direction) may gradually reduce toward the lower metal wiring layer **130** or the substrate **110**.

[0055] In a view from above (on an X-Y plane), the pair of first contact sidewalls **180VS** of the conductive contact plug **180C** may extend along extension lines of a pair of first straight lines (e.g., a pair of first dashed lines **LU** in FIGS. 1A and 2), along which the pair of upper line sidewalls **180LS** of the upper metal wiring layer **180L** corresponding thereto pass.

[0056] Each of the plurality of lower metal wiring layers **130** may include a pair of lower line sidewalls (refer to **130S** in FIGS. 1C and 2), which are opposite to each other in the second lateral direction (Y direction). In a view from above (on an X-Y plane), of the pair of second contact sidewalls **180TS** of the conductive contact plug **180C**, portions closest to the upper metal wiring layer **180L** may extend along extension lines of a pair of second straight lines (e.g., a pair of second dashed lines **LL** in FIGS. 1A and 2), along which the pair of lower line sidewalls **130S** of the lower metal wiring layer **130** corresponding thereto pass.

[0057] In some example embodiments, in a view from above (on an X-Y plane), a planar shape of the conductive contact plug **180C** may be the same as a planar shape of a region where the lower metal wiring layer **130** corresponding thereto overlaps the upper metal wiring layer **180L**.

corresponding thereto in the vertical direction (Z direction). For example, as shown in FIG. 1A, a planar shape of the first conductive contact plug **180CA** may be the same as a planar shape of a region where the first lower metal wiring layer **130A** overlaps the first upper metal wiring layer **180LA** in the vertical direction (Z direction). In addition, a planar shape of the second conductive contact plug **180CB** may be the same as a planar shape of a region where the second lower metal wiring layer **130B** overlaps the second upper metal wiring layer **180LB** in the vertical direction (Z direction).

[0058] In a view from above (on an X-Y plane), the IC device **100** described with reference to FIGS. 1A, 1B, 1C, and 2 may include the conductive contact plug **180C**, which extends in the vertical direction (Z direction) between the lower metal wiring layer **130** and the upper metal wiring layer **180L** to connect the lower metal wiring layer **130** to the upper metal wiring layer **180L** in a region where the lower metal wiring layer **130** intersects the upper metal wiring layer **180L**, and the conductive contact plug **180C** may have the same planar shape (e.g., a tetragonal planar shape) as the planar shape of a region where the lower metal wiring layer **130** overlaps the upper metal wiring layer **180L** in the vertical direction (Z direction). Accordingly, a planar size of the conductive contact plug **180C** configured to connect the lower metal wiring layer **130** to the upper metal wiring layer **180L** may be increased or maximized as much as possible without undesired area loss within a limited area to reduce or minimize contact resistance. Furthermore, by increasing a smallest separation distance between adjacent ones of the plurality of conductive contact plugs **180C** (e.g., a smallest separation distance **D1** between the first conductive contact plug **180CA** and the second conductive contact plug **180CB** in FIG. 1A), a sufficient insulation distance between adjacent ones of the plurality of conductive contact plugs **180C** may be ensured, and thus, the occurrence of an undesired short between adjacent ones of the plurality of conductive contact plugs **180C** may be reduced or prevented. Therefore, reliability of electrical connection between the lower metal wiring layer **130** and the upper metal wiring layer **180L** through the conductive contact plug **180C** may improve, and reliability of the IC device **100** may improve.

[0059] FIG. 3A is a plan layout diagram of an IC device **200A** according to an example embodiment. FIG. 3B is a cross-sectional view taken along line X1-X1' of FIG. 3A. FIG. 3C is a cross-sectional view taken along line Y1-Y1' of FIG. 3A. FIG. 4 is a partial perspective view of some components of the IC device **200A**. In FIGS. 3A, 3B, 3C, and 4, the same reference numerals are used to denote the same elements as in FIGS. 1A, 1B, 1C, and 2, and detailed descriptions thereof are omitted.

[0060] Referring to FIGS. 3A, 3B, 3C, and 4, the IC device **200A** may have the same or substantially similar configuration as the IC device **100** described with reference to FIGS. 1A, 1B, 1C, and 2. However, the IC device **200A** may include a plurality of upper metal wiring structures **280A**. Each of the plurality of upper metal wiring structures **280A** may include an upper metal wiring layer **280L** and a conductive contact plug **280C** integrally connected to the upper metal wiring layer **280L**. The conductive contact plug **280C** may include a main contact portion **280M** covering a top surface of the lower metal wiring layer **130** and a protruding contact portion **280P** covering a sidewall of the lower metal wiring layer **130**. The protruding contact portion

**280P** may be between the lower metal wiring layer **130** and the lower insulating film **126**. That is, the conductive contact plug **280C** may cover the top surface and the sidewall of the lower metal wiring layer **130** corresponding thereto.

[0061] Each of a plurality of conductive contact plugs **280C** may include a pair of first contact sidewalls **280VS** and a pair of second contact sidewalls **280TS**. The pair of first contact sidewalls **280VS** may be opposite to each other in the first lateral direction (X direction) and face the upper insulating film **140**. The pair of second contact sidewalls **280TS** may be opposite to each other in the second lateral direction (Y direction) and face the upper insulating film **140**.

[0062] In each of the plurality of conductive contact plugs **280C**, each of the pair of first contact sidewalls **280VS** may extend in the vertical direction (Z direction) on a plane (Y-Z plane) that is perpendicular to a main surface **110M** of a substrate **110**. Each of the pair of first contact sidewalls **280VS** may extend in the vertical direction (Z direction) from one upper line sidewall **280LS** adjacent thereto, from among a pair of upper line sidewalls (refer to **280LS** in FIGS. 3B and 4) included in a corresponding one of a plurality of upper metal wiring layers **280L**, to a corresponding one of a plurality of lower metal wiring layers **130**.

[0063] In each of the plurality of conductive contact plugs **280C**, one of the pair of second contact sidewalls **280TS** may extend in a direction inclined with respect to the vertical direction (Z direction) from a bottom surface of a corresponding one of the plurality of upper metal wiring layers **280L** toward the top surface of a corresponding one of the plurality of lower metal wiring layers **130**. From among the pair of second contact sidewalls **280TS**, another second contact sidewall **280TS** may extend in a direction inclined with respect to the vertical direction (Z direction) from the bottom surface of a corresponding one of the plurality of upper metal wiring layers **280L** toward the sidewall of a corresponding one of the plurality of lower metal wiring layers **130**. For example, as shown in FIGS. 3C and 4, each of the pair of second contact sidewalls **280TS** may have an inclined surface that gets close to a vertical central axis of the conductive contact plug **280C** toward (e.g., as it gets close to) a corresponding one of the lower metal wiring layers **130**.

[0064] In a view from above (on an X-Y plane), the pair of first contact sidewalls **280VS** of the conductive contact plug **280C** may extend along extension lines of a pair of first straight lines (e.g., a pair of first dashed lines **LU2** in FIGS. 3A and 4), along which the pair of upper line sidewalls **280LS** of the upper metal wiring layer **280L** extend. In a view from above (on an X-Y plane), the pair of second contact sidewalls **280TS** of the conductive contact plug **280C** may extend along extension lines of a pair of second straight lines (e.g., a pair of second dashed lines **LL2** in FIG. 3A), which extend in the first lateral direction (X direction), at a position shifted by a distance greater than 0 from the pair of lower line sidewalls **130S** of the lower metal wiring layer **130** corresponding thereto in a direction (e.g., a direction indicated by arrow **A2** in FIG. 3A) selected from the second lateral direction (Y direction) and a direction opposite to the second lateral direction (Y direction).

[0065] Detailed configurations of the plurality of upper metal wiring layers **280L** and the plurality of conductive contact plugs **280C** included in the plurality of upper metal wiring structures **280A** are the same as or substantially

similar to those of the plurality of upper metal wiring layers **180L** and the plurality of conductive contact plugs **180C**, which have been described with reference to FIGS. **1A**, **1B**, **1C**, and **2**, respectively.

**[0066]** In a view from above (on an X-Y plane), the IC device **200A** described with reference to FIGS. **3A**, **3B**, **3C**, and **4** may include the conductive contact plug **280C**, which extends in the vertical direction (Z direction) between the lower metal wiring layer **130** and the upper metal wiring layer **280L** to connect the lower metal wiring layer **130** to the upper metal wiring layer **280L** in a region where the lower metal wiring layer **130** intersects the upper metal wiring layer **280L**, and the conductive contact plug **280C** may have a tetragonal planar shape. Accordingly, a planar size of the conductive contact plug **280C** configured to connect the lower metal wiring layer **130** to the upper metal wiring layer **280L** may be increased or maximized as much as possible without undesired area loss within a limited area to reduce or minimize contact resistance. Furthermore, by increasing a smallest separation distance between adjacent ones of the plurality of conductive contact plugs **280C** (e.g., a smallest separation distance **D2A** between two adjacent conductive contact plugs **280C** in FIG. **3A**), a sufficient insulation distance between two adjacent ones of the plurality of conductive contact plugs **280C** may be ensured, and thus, the occurrence of an undesired short between adjacent ones of the plurality of conductive contact plugs **280C** may be reduced or prevented. Therefore, reliability of electrical connection between the lower metal wiring layer **130** and the upper metal wiring layer **280L** through the conductive contact plug **280C** may improve, and reliability of the IC device **200A** may improve.

**[0067]** FIG. **5A** is a plan layout diagram of an IC device **200B** according to an example embodiment. FIG. **5B** is a cross-sectional view taken along lines **Y1-Y1'** and **Y2-Y2'** of FIG. **5A**. In FIGS. **5A** and **5B**, the same reference numerals are used to denote the same elements as in FIGS. **1A** to **4**, and detailed descriptions thereof are omitted.

**[0068]** Referring to FIGS. **5A** and **5B**, the IC device **200B** may have the same or substantially similar configuration as the IC device **100** described with reference to FIGS. **1A**, **1B**, **1C**, and **2**. However, the IC device **200B** may include a plurality of first upper metal wiring structures **280B1** and a plurality of second upper metal wiring structures **280B2**.

**[0069]** Each of the plurality of first upper metal wiring structures **280B1** may include an upper metal wiring layer **280L** and a first conductive contact plug **280C1** integrally connected to the upper metal wiring layer **280L**. Each of the plurality of second upper metal wiring structures **280B2** may include an upper metal wiring layer **280L** and a second conductive contact plug **280C2** integrally connected to the upper metal wiring layer **280L**. Each of the first conductive contact plug **280C1** and the second conductive contact plug **280C2** may include a main contact portion **280M** covering a top surface of a lower metal wiring layer **130** and a protruding contact portion **280P** covering a sidewall of the lower metal wiring layer **130**. The protruding contact portion **280P** may be between the lower metal wiring layer **130** and the lower insulating film **126**. That is, each of the first conductive contact plug **280C1** and the second conductive contact plug **280C2** may cover the top surface and the sidewall of the lower metal wiring layer **130** corresponding thereto.

**[0070]** Similar to the plurality of conductive contact plugs **280C** described with reference to FIGS. **3A**, **3B**, **3C**, and **4**, each of a plurality of first conductive contact plugs **280C1** and a plurality of second conductive contact plugs **280C2** may have a pair of first contact sidewalls (corresponding to the pair of first contact sidewalls **280VS** shown in FIGS. **3B** and **4**), which are opposite to each other in a first lateral direction (X direction) and face the upper insulating film **140**, and each of the pair of first contact sidewalls **280VS** may extend in a vertical direction (Z direction) on a plane (Y-Z plane) that is perpendicular to the main surface **110M** of the substrate **110**. Each of the pair of first contact sidewalls may extend in the vertical direction (Z direction) from one upper line sidewall adjacent thereto, from among a pair of upper line sidewalls (corresponding to the pair of upper line sidewalls **280LS** shown in FIGS. **3B** and **4**) included in the upper metal wiring layer **280L** of a corresponding one of a plurality of upper metal wiring layers **280L**, to a corresponding one of the plurality of lower metal wiring layers **130**.

**[0071]** As shown in FIG. **5B**, each of the plurality of first conductive contact plugs **280C1** and the plurality of second conductive contact plugs **280C2** may include a pair of second contact sidewalls **280TS**, which are opposite to each other in the second lateral direction (Y direction) and face the upper insulating film **140**. In each of the plurality of first conductive contact plugs **280C1** and the plurality of second conductive contact plugs **280C2**, detailed configurations of the pair of first contact sidewalls are the same as or substantially similar to those of the pair of first contact sidewalls **280VS** included in the conductive contact plug **280C** described with reference to FIGS. **3A** and **3C**.

**[0072]** In a view from above (on an X-Y plane), the pair of first contact sidewalls of each of the plurality of first conductive contact plugs **280C1** and the plurality of second conductive contact plugs **280C2** may extend along extension lines of a pair of first straight lines (e.g., a pair of first dashed lines **LU2** in FIG. **5A**), along which the pair of upper line sidewalls **280LS** of the upper metal wiring layer **280L** corresponding thereto pass.

**[0073]** In a view from above (on an X-Y plane), the pair of second contact sidewalls **280TS** of each of the plurality of first conductive contact plugs **280C1** may extend along extension lines of a pair of second straight lines (e.g., a pair of second dashed lines **LL2A** in FIG. **5A**), which extend in the first lateral direction (X direction), at a position shifted by a distance greater than 0 from the pair of lower line sidewalls **130S** of the lower metal wiring layer **130** corresponding thereto in a direction (e.g., a direction indicated by arrow **A2A** in FIG. **5A**) opposite to the second lateral direction (Y direction).

**[0074]** In a view from above (on an X-Y plane), the pair of second contact sidewalls **280TS** of each of the plurality of second conductive contact plugs **280C2** may extend along extension lines of a pair of third straight lines (e.g., a pair of third dashed lines **LL2B** in FIG. **5A**), which extend in the first lateral direction (X direction), at a position shifted by a distance greater than 0 from the pair of lower line sidewalls **130S** of the lower metal wiring layer **130** corresponding thereto in the second lateral direction (Y direction) (e.g., a direction indicated by arrow **A2B** in FIG. **5A**).

**[0075]** Detailed configurations of the plurality of upper metal wiring layers **280L** included in the plurality of first upper metal wiring structures **280B1** and the plurality of

second upper metal wiring structures **280B2**, the plurality of first conductive contact plugs **280C1**, and the plurality of second conductive contact plugs **280C2** are respectively and the same as or substantially similar to those of the plurality of upper metal wiring layers **180L**) and the plurality of conductive contact plugs **180C**, which have been described above with reference to FIGS. **1A**, **1B**, **1C**, and **2**.

[**0076**] In a view from above (on an X-Y plane), the IC device **200B** described with reference to FIGS. **5A** and **5B** may include the first conductive contact plug **280C1** and the second conductive contact plug **280C2**, each of which extends in the vertical direction (Z direction) between a selected one of the plurality of lower metal wiring layers **130** and a selected one of the plurality of upper metal wiring layers **280L** to connect the selected lower metal wiring layer **130** to the selected upper metal wiring layer **280L** in a region where the plurality of lower metal wiring layers **130** intersect the plurality of upper metal wiring layers **280L**, and each of the first conductive contact plug **280C1** and the second conductive contact plug **280C2** may have a tetragonal planar shape. Accordingly, a planar size of the first conductive contact plug **280C1** or the second conductive contact plug **280C2** configured to connect the lower metal wiring layer **130** to the upper metal wiring layer **280L** may be increased or maximized as much as possible without undesired area loss within a limited area to reduce or minimize contact resistance. Furthermore, by increasing a smallest separation distance between adjacent ones of a plurality of first conductive contact plugs **280C1** and a plurality of second conductive contact plugs **280C2** (e.g., a smallest separation distance **D2A** between the first conductive contact plug **280C1** and the second conductive contact plug **280C2** in FIG. **5A**), a sufficient insulation distance therebetween may be ensured, and thus, the occurrence of an undesired short between adjacent ones of the plurality of first conductive contact plugs **280C1** and the plurality of second conductive contact plugs **280C2** may be reduced or prevented. Therefore, reliability of electrical connection between the lower metal wiring layer **130** and the upper metal wiring layer **280L** through the first conductive contact plug **280C1** and/or the second conductive contact plug **280C2** may improve, and reliability of the IC device **200B** may improve.

[**0077**] FIGS. **6A** and **6B** are cross-sectional views of an IC device **300** according to an example embodiment. FIG. **6A** illustrates components in a portion corresponding to a cross-section taken along line **X1-X1'** of FIG. **1A** in the IC device **300**. FIG. **6B** illustrates components in a portion corresponding to a cross-section taken along line **Y1-Y1'** of FIG. **1A** in the IC device **300**. In FIGS. **6A** and **6B**, the same reference numerals are used to denote the same elements as in FIGS. **1A**, **1B**, **1C**, and **2**, and detailed descriptions thereof are omitted.

[**0078**] Referring to FIGS. **6A** and **6B**, the IC device **300** may have the same or substantially similar configuration as the IC device **100** described with reference to FIGS. **1A**, **1B**, **1C**, and **2**. However, the IC device **300** may include an upper insulating structure **ILS3** including an etch stop film **332** and an upper insulating film **340**.

[**0079**] In some example embodiments, the etch stop film **332** may have a multilayered structure in which a first insulating film containing metal, a second insulating film free from metal, and a third insulating film containing metal are sequentially stacked. Each of the first insulating film and

the third insulating film may include an aluminum oxide film, an aluminum nitride film, or a combination thereof. For example, each of the first insulating film and the third insulating film may include an aluminum oxide film, an aluminum nitride film, or a combination thereof. The second insulating film may include a silicon oxide film, a SiOC film, or a combination thereof. Thicknesses of the first insulating film and the third insulating film may be different from each other in a vertical direction (Z direction). In some example embodiments, in the vertical direction (Z direction), respective thicknesses of the first insulating film, the second insulating film, and the third insulating film may be different from each other. For example, a thickness of the third insulating film may be greater than a thickness of the first insulating film. However, the inventive concepts are not limited thereto, and each of the first insulating film, the second insulating film, and the third insulating film may be formed to various thicknesses as needed. In other example embodiments, the etch stop film **332** may have a single film structure including a metal-containing insulating film. For example, the etch stop film **332** may include an aluminum oxide film, an aluminum nitride film, or a combination thereof. In the upper insulating structure **ILS3**, a constituent material of the upper insulating film **340** may be the same as a constituent material of the upper insulating film **140**, which has been described with reference to FIGS. **1B** and **1C**.

[**0080**] Each of the plurality of conductive contact plugs **180C** included in a plurality of upper metal wiring structures **180** may pass through the upper insulating film **340** and the etch stop film **332** in the vertical direction (Z direction) and contact the lower metal wiring layer **130** corresponding thereto.

[**0081**] FIG. **7** is a plan layout diagram of an IC device **400** according to an example embodiment. FIG. **8** is a cross-sectional view taken along line **X1-X1'** of FIG. **7**. FIG. **9** is a cross-sectional view taken along line **Y1-Y1'** of FIG. **7**. The IC device **400** including a field-effect transistor (FET) having a gate-all-around structure, which includes an active region of a nanowire or nanosheet type and a gate surrounding the active region, is described with reference to FIGS. **7** to **9**. In FIGS. **7** to **9**, the same reference numerals are used to denote the same elements as in FIGS. **1A**, **1B**, **1C**, and **2**, and detailed descriptions thereof are omitted.

[**0082**] Referring to FIGS. **7** to **9**, the IC device **400** may include a plurality of fin-type active regions **F1** and a plurality of nanosheet stacks **NSS**. The plurality of fin-type active regions **F1** may protrude from a substrate **402** and extend lengthwise in a first lateral direction (X direction). The plurality of nanosheet stacks **NSS** may be apart upward from the plurality of fin-type active regions **F1** in a vertical direction (Z direction) and face fin top surfaces **FT** of the plurality of fin-type active regions **F1**. As used herein, the term “nanosheet” refers to a conductive structure having a cross-section that is substantially perpendicular to a direction in which current flows. The nanosheet may be interpreted as including a nanowire.

[**0083**] A trench **T1** defining the plurality of fin-type active regions **F1** may be formed in the substrate **402**. The trench **T1** may be filled by a device isolation film **412**. The substrate **402** may include a semiconductor, such as silicon (Si) or germanium (Ge), or a compound semiconductor, such as silicon germanium (SiGe), silicon carbide (SiC), gallium arsenide (GaAs), indium arsenide (InAs), indium gallium arsenide (InGaAs), or indium phosphide (InP). The substrate

**402** may include a conductive region, for example, a doped well or a doped structure. The device isolation film **412** may include an oxide film, a nitride film, or a combination thereof.

**[0084]** A plurality of gate lines **460** may be on the plurality of fin-type active regions **F1**. Each of the plurality of gate lines **460** may extend lengthwise in a second lateral direction (Y direction) that intersects the first lateral direction (X direction).

**[0085]** A plurality of nanosheet stacks **NSS** may be on the fin top surfaces **FT** of the plurality of fin-type active regions **F1**, respectively, in regions where the plurality of fin-type active regions **F1** intersect the plurality of gate lines **460**. Each of the plurality of nanosheet stacks **NSS** may include at least one nanosheet facing the fin top surface **FT** of the fin-type active region **F1** at a position apart from the fin top surface **FT** of the fin-type active region **F1** in the vertical direction (Z direction).

**[0086]** In some example embodiments, each of the plurality of nanosheet stacks **NSS** may include a first nanosheet **N1**, a second nanosheet **N2**, and a third nanosheet **N3**, which overlap each other in the vertical direction (Z direction) on the fin-type active region **F1**. Each of the plurality of gate lines **460** may surround the first nanosheet **N1**, the second nanosheet **N2**, and the third nanosheet **N3**, which overlap each other in the vertical direction (Z direction) and are included in the nanosheet stack **NSS**.

**[0087]** Each of the plurality of gate lines **460** may include a main gate portion **460M** and a plurality of sub-gate portions **460S**. The main gate portion **460M** may extend lengthwise in the second lateral direction (Y direction), while covering a top surface of the nanosheet stack **NSS**. The plurality of sub-gate portions **460S** may be integrally connected to the main gate portion **460M** and located between the first nanosheet **N1**, the second nanosheet **N2**, and the third nanosheet **N3** and between the first nanosheet **N1** and the fin-type active region **F1**, respectively. In the vertical direction (Z direction), a thickness of each of the plurality of sub-gate portions **460S** may be less than a thickness of the main gate portion **460M**.

**[0088]** A plurality of recesses **R1** may be formed in the fin-type active region **F1**. A lowermost surface of each of the plurality of recesses **R1** may be at a lower vertical level than the fin top surface **FT** of the fin-type active region **F1**. The plurality of source/drain regions **430** may be inside the plurality of recesses **R1**. Each of the plurality of source/drain regions **430** may be adjacent to at least one gate line **460** selected from the plurality of gate lines **460**. Each of the plurality of source/drain regions **430** may be in contact with the first nanosheet **N1**, the second nanosheet **N2**, and the third nanosheet **N3**, which are included in the nanosheet stack **NSS** adjacent thereto.

**[0089]** Each of the plurality of gate lines **460** may include metal, metal nitride, metal carbide, or a combination thereof. The metal may be selected from titanium (Ti), tungsten (W), ruthenium (Ru), niobium (Nb), molybdenum (Mo), hafnium (Hf), nickel (Ni), cobalt (Co), platinum (Pt), ytterbium (Yb), terbium (Tb), dysprosium (Dy), erbium (Er), and palladium (Pd). The metal nitride may be selected from TiN and TaN. The metal carbide may include titanium aluminum carbide (TiAlC). However, a constituent material of the plurality of gate lines **460** is not limited to the examples described above. Each of the plurality of gate lines **460** may further include a gap-fill metal film. The gap-fill metal film may

include a tungsten (W) film and an aluminum (Al) film. In some example embodiments, each of the plurality of gate lines **460** may include a TiN film, a stack structure of TiAlC/TiN/W, a stack structure of TiN/TaN/TiAlC/TiN/W, or a stack structure of TiN/TaN/TiN/TiAlC/TiN/W, without being limited thereto.

**[0090]** A gate dielectric film **452** may be between the nanosheet stack **NSS** and the gate line **460**. In some example embodiments, the gate dielectric film **452** may include a stack structure of an interface dielectric film and a high-k dielectric film. The interface dielectric film may include a low-k dielectric material film having a dielectric constant of about 9 or lower, for example, a silicon oxide film, a silicon oxynitride film, or a combination thereof. In some example embodiments, the interface dielectric film may be omitted. The high-k dielectric film may include a material having a higher dielectric constant than a silicon oxide film. For example, the high-k dielectric film may have a dielectric constant of about 10 to about 25. The high-k dielectric film may include hafnium oxide, without being limited thereto.

**[0091]** Both sidewalls of the gate line **460** may be covered by insulating spacers **418**. The insulating spacers **418** may cover both sidewalls of the main gate portion **460M** on a top surface of each of the plurality of nanosheet stacks **NSS**. The insulating spacers **418** may be apart from the gate line **460** with the gate dielectric film **452** therebetween. The insulating spacers **418** may include silicon nitride, silicon oxide, silicon carbonitride (SiCN), silicon boronitride (SiBN), silicon oxynitride (SiON), silicon oxycarbonitride (SiOCN), silicon boron carbonitride (SiBCN), silicon oxycarbide (SiOC), or a combination thereof.

**[0092]** A top surface of each of the gate dielectric film **452**, the gate line **460**, and the insulating spacers **418** may be covered by a capping insulating pattern **468**. The capping insulating pattern **468** may contact a top surface of each of the gate dielectric film **452**, the gate line **460**, and the insulating spacers **418**. The capping insulating pattern **468** may include a silicon nitride film.

**[0093]** Both sidewalls of each of the plurality of sub-gate portions **460S** may be apart from the source/drain region **430** with the gate dielectric film **452** therebetween. The gate dielectric film **452** may be between the sub-gate portion **460S** included in the gate line **460** and each of the first nanosheet **N1**, the second nanosheet **N2**, and the third nanosheet **N3** and between the sub-gate portion **460S** included in the gate line **460** and the source/drain region **430**.

**[0094]** A plurality of nanosheet transistors may be formed in portions where the plurality of fin-type active regions **F1** intersect the plurality of gate lines **460** on the substrate **402**. Each of the first nanosheet **N1**, the second nanosheet **N2**, and the third nanosheet **N3** included in the nanosheet stack **NSS** may have a channel region. In some example embodiments, each of the first nanosheet **N1**, the second nanosheet **N2**, and the third nanosheet **N3** included in the nanosheet stack **NSS** may include a silicon (Si) layer, a silicon germanium (SiGe) layer, or a combination thereof.

**[0095]** A metal silicide film **472** may be formed on a top surface of each of the plurality of source/drain regions **430**. The metal silicide film **472** may include metal, which includes Ti, W, Ru, Nb, Mo, Hf, Ni, Co, Pt, Yb, Tb, Dy, Er, or Pd. For example, the metal silicide film **472** may include titanium silicide, without being limited thereto.

[0096] An insulating liner 442 and an inter-gate dielectric film 444 may be sequentially on the plurality of source/drain regions 430 and a plurality of metal silicide films 472. In some example embodiments, the insulating liner 442 may include silicon nitride (SiN), SiCN, SiBN, SiON, SiOCN, SiBCN, or a combination thereof, and the inter-gate dielectric film 444 may include a silicon oxide film, without being limited thereto.

[0097] A plurality of source/drain contacts CA may be on the plurality of source/drain regions 430. Each of the plurality of source/drain contacts CA may pass through the inter-gate dielectric film 444 and the insulating liner 442 in the vertical direction (Z direction) and contact the metal silicide film 472. Each of the plurality of source/drain contacts CA may be electrically connectable to the source/drain region 430 through the metal silicide film 472. Each of the plurality of source/drain contacts CA may be apart from the main gate portion 460M with the insulating spacers 418 therebetween in the first lateral direction (X direction).

[0098] Each of the plurality of source/drain contacts CA may include a conductive barrier film 474 and a contact plug 476, which are sequentially stacked on the metal silicide film 472. The conductive barrier film 474 may surround and contact a bottom surface and a sidewall of the contact plug 476. In some example embodiments, the conductive barrier film 474 may include metal or metal nitride. For example, the conductive barrier film 474 may include titanium (Ti), tantalum (Ta), tungsten (W), titanium nitride (TiN), tantalum nitride (TaN), tungsten nitride (WN), tungsten carbonitride (WCN), titanium silicon nitride (TiSiN), tantalum silicon nitride (TaSiN), tungsten silicon nitride (WSiN), or a combination thereof. The contact plug 476 may include metal selected from molybdenum (Mo), copper (Cu), tungsten (W), cobalt (Co), ruthenium (Ru), manganese (Mn), titanium (Ti), tantalum (Ta), aluminum (Al), and a combination thereof.

[0099] A lower insulating structure 480 may be on a top surface of each of the plurality of source/drain contacts CA and a plurality of capping insulating patterns 468. The lower insulating structure 480 may include a lower etch stop film 482 and a first interlayer insulating film 484, which are sequentially stacked on the top surface of each of the plurality of capping insulating patterns 468. The lower etch stop film 482 may include silicon carbide (SiC), silicon nitride (SiN), nitrogen (N)-doped silicon carbide (SiC:N), silicon oxycarbide (SiOC), aluminum nitride (AlN), aluminum oxynitride (AlON), aluminum oxide (AlO), aluminum oxycarbide (AlOC), or a combination thereof. A constituent material of the first interlayer insulating film 484 may be the same as or substantially similar to that of the first interlayer insulating film 114 described with reference to FIG. 2.

[0100] As shown in FIG. 8, a plurality of source/drain via contacts VA may be on the plurality of source/drain contacts CA, respectively. Each of the plurality of source/drain via contacts VA may pass through the lower insulating structure 480 and contact the source/drain contact CA. Each of the plurality of source/drain regions 430 may be electrically connected to the source/drain via contact VA through the metal silicide film 472 and the source/drain contact CA.

[0101] As shown in FIG. 9, a gate contact CB may be on the gate line 460. The gate contact CB may pass through the lower insulating structure 480 and the capping insulating pattern 468 in the vertical direction (Z direction) and be connected to the gate line 460.

[0102] Each of the plurality of source/drain via contacts VA and the gate contact CB may include a contact plug, which includes molybdenum (Mo), copper (Cu), tungsten (W), cobalt (Co), ruthenium (Ru), manganese (Mn), titanium (Ti), tantalum (Ta), aluminum (Al), a combination thereof, or an alloy thereof, but a constituent material of the contact plug is not limited thereto. In some example embodiments, each of the plurality of source/drain via contacts VA and the gate contact CB may further include a conductive barrier pattern surrounding a portion of the contact plug. The conductive barrier pattern included in each of the plurality of source/drain via contacts VA and the gate contact CB may include metal or metal nitride. For example, the conductive barrier pattern may include Ti, Ta, W, TiN, TaN, WN, WCN, TiSiN, TaSiN, WSiN, or a combination thereof, without being limited thereto.

[0103] A second lower etch stop film 122 and a second interlayer insulating film 124 may be sequentially stacked on each of the lower insulating structure 480, the source/drain via contact VA, and the gate contact CB. A lower insulating film 126, a plurality of lower metal wiring layers 130, an upper insulating film 140, and a plurality of upper metal wiring structures 180 may be on the second interlayer insulating film 124. Each of the plurality of upper metal wiring structures 180 may include an upper metal wiring layer 180L and a conductive contact plug 180C integrally connected to the upper metal wiring layer 180L.

[0104] Each of the plurality of conductive contact plugs 180C may include a pair of first contact sidewalls 180VS and a pair of second contact sidewalls 180TS. The pair of first contact sidewalls 180VS may be opposite to each other in the first lateral direction (X direction) and face the upper insulating film 140. The pair of second contact sidewalls 180TS may be opposite to each other in the second lateral direction (Y direction) and face the upper insulating film 140. Each of the pair of first contact sidewalls 180VS may extend in the vertical direction (Z direction), which is that is perpendicular to a main surface 110M of the substrate 110, on a plane (Y-Z plane). From among the pair of second contact sidewalls 180TS, at least one second contact sidewall 180TS may extend in a direction inclined with respect to the vertical direction (Z direction) from a bottom surface of a corresponding one of a plurality of upper metal wiring layers 180L toward a corresponding one of the plurality of lower metal wiring layers 130. Detailed configurations and effects of the plurality of upper metal wiring structures 180 are the same as those described with reference to FIGS. 1A, 1B, 1C, and 2.

[0105] FIG. 10 is a cross-sectional view of an IC device 500 according to an example embodiment. FIG. 10 illustrates components in a portion corresponding to a cross-section taken along line Y1-Y1' of FIG. 1A in the IC device 500. In FIG. 10, the same reference numerals are used to denote the same elements as in FIGS. 1A to 4, and detailed descriptions thereof are omitted.

[0106] Referring to FIG. 10, the IC device 500 may have the same or substantially similar configuration as the IC device 400 described with reference to FIGS. 6 to 9. However, the IC device 500 may include a plurality of upper metal wiring structures 280A. Each of the plurality of upper metal wiring structures 280A may include an upper metal wiring layer 280L and a conductive contact plug 280C integrally connected to the upper metal wiring layer 280L. The conductive contact plug 280C may include a main

contact portion **280M** covering a top surface of a lower metal wiring layer **130** and a protruding contact portion **280P** covering a sidewall of the lower metal wiring layer **130**. The protruding contact portion **280P** may be between the lower metal wiring layer **130** and the lower insulating film **126**. That is, the conductive contact plug **280C** may cover the top surface and sidewall of the lower metal wiring layer **130** corresponding thereto. Detailed configurations and effects of the plurality of upper metal wiring structures **280A** are the same as those described with reference to FIGS. 1A, 1B, 1C, and 2.

[0107] In the IC devices **400**, **500** described with reference to FIGS. 7 to 10, similar to the IC device **100** described with reference to FIGS. 1A, 1B, 1C, and 2, a planar size of the conductive contact plug **180C** or **280C** configured to connect the lower metal wiring layer **130** to the upper metal wiring layer **180L** or **280L** may be increased maximized as much as possible without undesired area loss within a limited area to reduce or minimize contact resistance. Furthermore, by increasing a smallest separation distance between adjacent ones of the plurality of conductive contact plugs **180C** and **280C**, a sufficient insulation distance between adjacent ones of the plurality of conductive contact plugs **180C** and **280C** may be ensured, and thus, the occurrence of an undesired short between adjacent ones of the plurality of conductive contact plugs **180C** and **280C** may be reduced or prevented. Therefore, reliability of electrical connection between the lower metal wiring layer **130** and the upper metal wiring layer **180L** or **280L** through the conductive contact plug **180C** or **280C** may improve, and reliability of the IC device **200A** may improve.

[0108] FIGS. 11A to 20C are diagrams of process sequences of methods of manufacturing IC devices, according to an example embodiment. FIGS. 11A, 12A, 13A, 14A, 15A, 16A, 17A, 18A, 19A, and 20A are plan views of process sequences of methods of manufacturing IC devices, according to an example embodiment. FIGS. 11B, 12B, 13B, 14B, 15B, 16B, 17B, 18B, 19B, and 20B are cross-sectional views taken along lines X1-X1' of FIGS. 11A, 12A, 13A, 14A, 15A, 16A, 17A, 18A, 19A, and 20A, respectively. FIGS. 15C, 16C, 17C, 18C, 19C, and 20C are cross-sectional views taken along lines Y1-Y1' of FIGS. 15A, 16A, 17A, 18A, 19A, and 20A, respectively. An example of a method of manufacturing the IC device **100** described with reference to FIGS. 1A, 1B, 1C, and 2 is described with reference to FIGS. 11A to 20C. In FIGS. 11A to 20C, the same reference numerals are used to denote the same elements as in FIGS. 1A, 1B, 1C, and 2, and detailed descriptions thereof are omitted.

[0109] Referring to FIGS. 11A and 11B, a first lower etch stop film **112** and a first interlayer insulating film **114** may be formed on a substrate **110**, and a conductive structure **120** may be formed to pass through the first interlayer insulating film **114** and the first lower etch stop film **112** and electrically connectable to a conductive region (not shown) of the substrate **110**. The formation of the conductive structure **120** may include partially etching the first interlayer insulating film **114** and the first lower etch stop film **112** to form an opening and filling the opening with conductive materials. The conductive structure **120** may be electrically connected to the conductive region formed in the substrate **110**. In some other example embodiments, the conductive structure

**120** may be a source/drain region of a transistor, a source/drain contact, a via contact, or a gate contact, without being limited thereto.

[0110] A second lower etch stop film **122** and a second interlayer insulating film **124** may be formed on the first interlayer insulating film **114**. A lower insulating film **126** may be formed on the second interlayer insulating film **124**. A plurality of lower metal wiring layers **130** may be formed to pass through the lower insulating film **126** in a vertical direction (Z direction).

[0111] Referring to FIGS. 12A and 12B, an upper insulating film **140** having a planarized top surface may be formed on the lower insulating film **126** and the plurality of lower metal wiring layers **130**. Thereafter, a first hard mask pattern HM1 may be formed on the upper insulating film **140**. The first hard mask pattern HM1 may include a plurality of first openings H1 having planar shapes corresponding to planar shapes of a plurality of upper metal wiring layers (refer to **180L** in FIGS. 1A, 1B, 1C, and 2), respectively. The top surface of the upper insulating film **140** may be exposed through the plurality of first openings H1 formed in the first hard mask pattern HM1. In some example embodiments, the first hard mask pattern HM1 may include a metal-containing mask pattern. For example, the first hard mask pattern HM1 may include a titanium nitride (TiN) film, a tungsten (W) film, a tungsten (W)-doped carbon film, or a combination thereof, without being limited thereto.

[0112] Referring to FIGS. 13A and 13B, a planarized hard mask layer **150** may be formed on the resultant structure of FIGS. 12A and 12B. In some example embodiments, the planarized hard mask layer **150** may include a SOH (spin on hardmask (SOH) film, without being limited thereto.

[0113] An inorganic hard mask layer **160** may be formed on the planarized hard mask layer **150**. In some example embodiments, the inorganic hard mask layer **160** may include a silicon oxynitride (SiON) film, without being limited thereto.

[0114] A photoresist pattern RP may be formed on the inorganic hard mask layer **160**. A plurality of second openings H2 may be formed in the photoresist pattern RP. The plurality of second openings H2 may be located on the plurality of lower metal wiring layers **130** to correspond to regions where a plurality of conductive contact plugs **180C** are to be formed. That is, the plurality of second openings H2 formed in the photoresist pattern RP may overlap the plurality of first openings H1 formed in the first hard mask pattern HM1 in the vertical direction (Z direction).

[0115] In a first lateral direction (X direction), a planar size (X-Y planar size) of each of the plurality of second openings H2 formed in the photoresist pattern RP may be less than a planar size (X-Y planar size) of each of the plurality of conductive contact plugs **180C**. The inorganic hard mask layer **160** may be exposed through the plurality of second openings H2. In some example embodiments, the photoresist pattern RP may be formed by exposure to extreme ultraviolet (EUV) light having a wavelength of 13.5 nm, without being limited thereto.

[0116] In some example embodiments, in the first lateral direction (X direction), a width D2X of each of the plurality of second openings H2 formed in the photoresist pattern RP may be less than a width D1X of each of the plurality of first openings H1 formed in the first hard mask pattern HM1. In a second lateral direction (Y direction), a width D2Y (see FIG. 14A) of each of the plurality of second openings H2



formed in the photoresist pattern RP may be substantially equal to a width of the lower metal wiring layer 130.

[0117] Referring to FIGS. 14A and 14B, in the resultant structure of FIGS. 13A and 13B, the inorganic hard mask layer 160 may be etched by using the photoresist pattern RP as an etch mask to form an inorganic hard mask pattern 160P. Thus, the plurality of second openings H2 may extend to a space passing through the inorganic hard mask pattern 160P in the vertical direction (Z direction), and the planarized hard mask layer 150 may be exposed through the plurality of second openings H2.

[0118] Referring to FIGS. 15A, 15B, and 15C, in the resultant structure of FIGS. 14A and 14B, from among the width D2X of each of the plurality of second openings H2 in the first lateral direction (X direction) and the width D2Y of each of the plurality of second openings H2 in the second lateral direction (Y direction), only the width D2X in the first lateral direction (X direction) may be selectively increased. Thus, a second hard mask pattern HM2 having a plurality of extended second openings EH2 may be obtained from the inorganic hard mask pattern 160P. The plurality of extended second openings EH2 may pass through the photoresist pattern RP and the second hard mask pattern HM2 in a vertical direction.

[0119] A width ED2X of each of the plurality of extended second openings EH2 in the first lateral direction (X direction) may be greater than a width D1X of each of the plurality of first openings H1 in the first lateral direction (X direction). A width ED2Y of each of the plurality of extended second openings EH2 in the second lateral direction (Y direction) may be substantially equal to a width D2Y of each of the plurality of first openings H1 in the second lateral direction (Y direction). Of an outline of each of the plurality of extended second openings EH2, portions that intersect the first opening H1 of the first hard mask pattern HM1 in the first lateral direction (X direction) may include straight lines that follow the first lateral direction (X direction).

[0120] In some example embodiments, to form the plurality of extended second openings EH2 by selectively increasing the width D2X of each of the plurality of second openings H2 in the first lateral direction (X direction), an etching process in an oblique direction or a tilted direction (hereinafter, a tilting etch process) may be performed. To perform the tilted etch process, an etching process using ion beams (hereinafter, an ion beam etch process) may be performed. In some example embodiments, the ion beam etch process may be an ion beam etch process using a reactive gas (e.g., a fluorine (F)-based gas) as an ion source. During the ion beam etch process, argon (Ar) may be used as the ion source in addition to the fluorine-based gas. Fluorocarbon-based gases, such as CF<sub>4</sub>, C<sub>2</sub>F<sub>6</sub>, C<sub>3</sub>F<sub>8</sub>, C<sub>4</sub>F<sub>6</sub> gas, C<sub>4</sub>F<sub>8</sub>, may be used as the fluorine-based gas, without being limited thereto.

[0121] In some example embodiments, to form the plurality of extended second openings EH2 by selectively increasing the width D2X of each of the plurality of second openings H2 in the first lateral direction (X direction), as shown in FIG. 15B, the ion beam etch process may be performed by varying an ion beam incidence direction in a direction selected within a range between a direction of a dashed arrow IB11 and a direction of a dashed arrow IB13 and a range between a direction of a dashed arrow IB12 and a direction of a dashed arrow IB14 in the first lateral

direction (X direction). During the ion beam etch process, a variation range of the ion beam incidence direction in the first lateral direction (X direction) may be selected within a range from a first angle AG1 to a second angle AG2. The first angle may be an angle greater than 45° with respect to a straight line parallel to a main surface 110M of the substrate 110, and the second angle AG2 may be an angle perpendicular to the main surface 110M of the substrate 110. For example, during the ion beam etch process, a variation range of the ion beam incidence direction in the first lateral direction (X direction) may be selected within a range of about 50° to about 90° with respect to a straight line parallel to the main surface 110M of the substrate 110.

[0122] Unlike in the first lateral direction (X direction), in the second lateral direction (Y direction), the ion beam etch process may be performed while ion beams are incident in a direction of dashed arrows IB, which is perpendicular to the main surface 110M of the substrate, as illustrated in FIG. 15C.

[0123] Referring to FIGS. 16A, 16B, and 16C, the planarized hard mask layer 150 may be etched by using the second hard mask pattern HM2 as an etch mask, and thus, a hard mask pattern 150P having a plurality of elliptical holes 150H exposing a portion of the first hard mask pattern HM1 may be formed. As used herein, the hard mask pattern 150P may also be referred to as a third hard mask pattern. Of an outline of each of the plurality of elliptical holes 150H of the hard mask pattern 150P, portions that intersect the first opening H1 of the first hard mask pattern HM1 in the first lateral direction (X direction) may include straight lines that follow the first lateral direction (X direction).

[0124] After the hard mask pattern 150P including the plurality of elliptical holes 150H is formed, residues of unnecessary films (e.g., the second hard mask pattern HM2 and the photoresist pattern RP) that remain on the hard mask pattern 150P may be removed. In some example embodiments, the photoresist pattern RP may be removed in advance before an etching process of forming the hard mask pattern 150P is performed.

[0125] Referring to FIGS. 17A, 17B, and 17C, in the resultant structure of FIGS. 16A, 16B, and 16C, the upper insulating film 140 may be etched by a partial thickness by means of an anisotropic etching process using the hard mask pattern 150P and the first hard mask pattern HM1 as etch masks, and thus, a plurality of recess holes 140R may be formed in partial regions of the upper insulating film 140.

[0126] In some example embodiments, the plurality of recess holes 140R may be formed in the upper insulating film 140 by using a plasma-enhanced atomic layer etching (PEALE) process. In some example embodiments, the formation of the plurality of recess holes 140R in the upper insulating film 140 may include supplying an etch gas along with Ar gas onto a surface to be etched in a reaction chamber in which the resultant structure of FIGS. 16A, 16B, and 16C is loaded, purging the inside of the reaction chamber into which the etch gas is supplied by using the Ar gas, supplying a reactive gas along with Ar gas into the reaction chamber, and purging the inside of the reaction chamber into which the reactive gas is supplied. In some example embodiments, the etch gas may include a fluorocarbon compound. For example, the etch gas may include CHF<sub>3</sub>, CH<sub>2</sub>F<sub>2</sub>, CH<sub>3</sub>F, CF<sub>4</sub>, C<sub>2</sub>F<sub>6</sub>, C<sub>4</sub>F<sub>8</sub>, C<sub>4</sub>F<sub>6</sub>, or a combination thereof, without

being limited thereto. The reactive gas may include  $O_2$ ,  $CO_2$ ,  $N_2O$ , or a combination thereof, without being limited thereto.

[0127] During the supplying of the etch gas along with the Ar gas into the reaction chamber, pulsed radio-frequency (RF) power may be applied to the reaction chamber to generate reactive species of the Ar gas and bring a surface of the upper insulating film 140 on which the etch gas is chemisorbed, into contact with the reactive species such that the upper insulating film 140 is etched.

[0128] While the upper insulating film 140 is being anisotropically etched to form the plurality of recess holes 140R, when viewed from a cross-section taken in the first lateral direction (X direction) as shown in FIG. 17B, an etch gas for etching the upper insulating film 140 and/or a reactive gas may be supplied through a plurality of elliptical holes 150H having a relatively great width in the first lateral direction (X direction). In this case, a relatively large amount of etch gas and/or reactive gas may reach the upper insulating film 140, which is a film to be etched, through the plurality of elliptical holes 150H having the relatively great width in the first lateral direction (X direction). Thus, in a cross-section taken in the first lateral direction (X direction), the upper insulating film 140 may be etched to have a vertical sidewall 140VS, which is aligned with a sidewall of the first hard mask pattern HM1 and extends in the vertical direction (Z direction). Thus, a width of each of the plurality of recess holes 140R in the first lateral direction (X direction) may be defined by the vertical sidewall 140VS that extends in the vertical direction (Z direction).

[0129] In contrast, while the upper insulating film 140 is being anisotropically etched to form the plurality of recess holes 140R, when viewed from a cross-section taken in the second lateral direction (Y direction) as shown in FIG. 17C, an etch gas for etching the upper insulating film 140 and/or a reactive gas may be supplied through a plurality of elliptical holes 150H having a relatively small width in the second lateral direction (Y direction). In this case, a relatively small amount of etch gas and/or reactive gas may reach the upper insulating film 140, which is the film to be etched, through the plurality of elliptical holes 150H having the relatively small width in the second lateral direction (Y direction). As a result, after the plurality of recess holes 140R are formed in the upper insulating film 140, in a cross-section taken in the second lateral direction (Y direction), an inclined sidewall 140TS defining a width of each of the plurality of recess holes 140R in the second lateral direction (Y direction) may be formed in the upper insulating film 140. A width of each of the plurality of recess holes 140R in the second lateral direction (Y direction) may reduce toward the substrate 110.

[0130] Referring to FIGS. 18A, 18B, and 18C, the hard mask pattern 150P may be removed from the resultant structure of FIGS. 17A, 17B, and 17C to expose a top surface 140T of the upper insulating film 140. When the hard mask pattern 150P includes a spin-on-hardmask (SOH) film, the hard mask pattern 150P may be removed by using an ashing process and a strip process.

[0131] Referring to FIGS. 19A, 19B, and 19C, in the resultant structure of FIGS. 18A, 18B, and 18C, the upper insulating film 140 may be etched by using the first hard mask pattern HM1 as an etch mask, and thus, a plurality of line spaces LH and a plurality of via spaces VH may be formed in the upper insulating film 140. The plurality of line

spaces LH may be the resultant structure obtained by etching a portion of the upper insulating film 140 from the top surface 140T of the upper insulating film 140, which is exposed in the resultant structure of FIGS. 18B and 18C. The plurality of line spaces LH may be apart from the plurality of lower metal wiring layers 130 and the lower insulating film 126 in the vertical direction (Z direction). The plurality of via spaces VH may be the resultant structure obtained by etching a portion of the upper insulating film 140 from the plurality of recess holes 140R in the resultant structure of FIGS. 18B and 18C. The lower metal wiring layer 130 may be exposed through each of the plurality of via spaces VH.

[0132] Similar to the description provided with reference to FIGS. 18A, 18B, and 18C, the plurality of via spaces VH may be defined by the vertical sidewall 140VS of the upper insulating film 140, which is aligned with the sidewall of the first hard mask pattern HM1 and extends in the vertical direction (Z direction), in the cross-section taken in the first lateral direction (X direction), and may be defined by the inclined sidewall 140TS of the upper insulating film 140 in a cross-section taken in the second lateral direction (Y direction). A width of each of the plurality of via spaces VH in the second lateral direction (Y direction) may reduce toward the substrate 110.

[0133] Referring to FIGS. 20A, 20B, and 20C, in the resultant structure of FIGS. 19A, 19B, and 19C, a metal-containing conductive layer may be formed to fill the plurality of via spaces VH and the plurality of line spaces LH. The metal-containing conductive layer may include a metal plug and a conductive barrier film surrounding a sidewall and a bottom surface of the metal plug. The metal plug may include Cu, W, Mo, Ru, Co, Al, or a combination thereof. For example, the metal plug may include Cu. The conductive barrier film may include a TiN film, a TaN film, a Co film, or a combination thereof. For example, when the metal plug includes Cu, the conductive barrier film may include a multilayered structure including a TaN film and a Co film, without being limited thereto.

[0134] Thereafter, the metal-containing conductive layer may be planarized such that the top surface of the upper insulating film 140 is exposed, and thus, a plurality of upper metal wiring structures 180 may be formed from the metal-containing conductive layer.

[0135] FIG. 21 is a plan view illustrating a method of manufacturing an IC device, according to an example embodiment. An example of a method of manufacturing the IC device 200A shown in FIGS. 3A, 3B, 3C, and 4 is described with reference to FIG. 21. In FIG. 21, the same reference numerals are used to denote the same elements as in FIGS. 1A to 20C, and detailed descriptions thereof are omitted.

[0136] Referring to FIG. 21, the processes described with reference to FIGS. 11A to 14B may be performed. However, a photoresist pattern RP2A may be formed instead of the photoresist pattern RP in the process described with reference to FIGS. 13A and 13B. A plurality of second openings H2A may be formed in the photoresist pattern RP2A. The plurality of second openings H2A may be located to correspond to positions of a plurality of conductive contact plugs (refer to 280C in FIGS. 3A, 3B, 3C, and 4), which are to be formed on a plurality of lower metal wiring layers 130. In a first lateral direction (X direction), a planar size (X-Y planar size) of each of the plurality of second openings H2A may

be less than a planar size (X-Y planar size) of each of the plurality of conductive contact plugs **280C**.

**[0137]** In a view from above (on an X-Y plane), each of the plurality of second openings **H2A** formed in the photoresist pattern **RP2A** may be formed at a position shifted by a distance greater than 0 from the pair of lower line sidewalls (refer to **130S** in FIGS. **3C** and **4**) of the lower metal wiring layer **130** corresponding thereto in a direction (e.g., a direction indicated by arrow **A2** in FIG. **21**) selected from the second lateral direction (Y direction) and a direction opposite to the second lateral direction (Y direction).

**[0138]** Afterwards, according to a process similar to that described with reference to FIGS. **14A** and **14B**, the inorganic hard mask layer (refer to **160** in FIGS. **13A** and **13B**) may be etched by using the photoresist pattern **RP2A** as an etch mask to form an inorganic hard mask pattern **160P**. Thus, the plurality of second openings **H2A** may extend to a space passing through the inorganic hard mask pattern **160P** in the vertical direction (Z direction), and the planarized hard mask layer **150** may be exposed through the plurality of second openings **H2A**. Thereafter, the processes described with reference to FIGS. **15A** to **20C** may be performed on the resultant structure of FIG. **21**, and thus, the IC device **200A** described with reference to FIGS. **3A**, **3B**, **3C**, and **4** may be manufactured.

**[0139]** FIG. **22** is a plan view of a method of manufacturing an IC device, according to an example embodiment. An example of a method of manufacturing the IC device shown in FIGS. **5A** and **5B** is described with reference to FIG. **22**. In FIG. **22**, the same reference numerals are used to denote the same elements as in FIGS. **1A** to **21**, and detailed descriptions thereof are omitted.

**[0140]** Referring to FIG. **22**, the processes described with reference to FIGS. **11A** to **14B** may be performed. However, a photoresist pattern **RP2B** may be formed instead of the photoresist pattern **RP** in the process described with reference to FIGS. **13A** and **13B**. A plurality of second openings **H2B** may be formed in the photoresist pattern **RP2B**. The plurality of second openings **H2BA** may be located to correspond to positions of a plurality of first conductive contact plugs (refer to **280C1** in FIGS. **5A** and **5B**) and a plurality of second conductive contact plugs (refer to **280C2** in FIGS. **5A** and **5B**), which are to be formed on a plurality of lower metal wiring layer **130**. A planar size (X-Y planar size) of each of the plurality of second openings **H2B** in a first lateral direction (X direction) may be less than a planar size (X-Y planar size) of each of a plurality of first conductive contact plugs **280C1** and a plurality of second conductive contact plugs **280C2**.

**[0141]** In a view from above (on an X-Y plane), each of some of the plurality of second openings **H2B** formed in the photoresist pattern **RP2B** may be formed at a position shifted by a distance greater than 0 from a pair of lower line sidewalls (refer to **130S** in FIG. **5B**) of the lower metal wiring layer **130** corresponding thereto in a direction (e.g., a direction indicated by arrow **A2A** in FIG. **22**) opposite to a second lateral direction (Y direction). In a view from above (on an X-Y plane), each of some others of the plurality of second openings **H2B** formed in the photoresist pattern **RP2B** may be formed at a position shifted by a distance greater than 0 from the pair of lower line sidewalls (refer to **130S** in FIG. **5B**) of the lower metal wiring layer **130**

corresponding thereto in the second lateral direction (Y direction) (e.g., a direction indicated by arrow **A2B** in FIG. **22**).

**[0142]** Subsequently, according to a process similar to that described with reference to FIGS. **14A** and **14B**, an inorganic hard mask layer (refer to **160** in FIGS. **13A** and **13B**) may be etched by using the photoresist pattern **RP2B** as an etch mask to form an inorganic hard mask pattern **160P**. As a result, the plurality of second openings **H2B** may extend to a space passing through the inorganic hard mask pattern **160P** in a vertical direction (Z direction), and the planarized hard mask layer **150** may be exposed through the plurality of second openings **H2B**. Thereafter, the processes described with reference to FIGS. **15A** to **20C** may be performed on the resultant structure of FIG. **22**, and thus, the IC device **200B** described with reference to FIGS. **5A** and **5B** may be manufactured.

**[0143]** Although the methods of manufacturing the IC devices **100**, **200A**, and **200B** shown in FIGS. **1A** to **5B** have been described with reference to FIGS. **11A** to **22**, it will be understood that the IC devices **300**, **400**, and **500** shown in FIGS. **6A** to **10** and IC devices having variously changed structures may be manufactured by applying various modifications and changes to the processes described with reference to FIGS. **11A** to **22** within the scope of the inventive concepts.

**[0144]** While the inventive concepts have been particularly shown and described with reference to some example embodiments thereof, it will be understood that various changes in form and details may be made therein without departing from the spirit and scope of the following claims.

1. An integrated circuit device comprising:
  - a lower insulating film on a substrate;
  - a lower metal wiring layer passing through the lower insulating film and extending lengthwise in a first lateral direction;
  - an upper insulating film on the lower insulating film and the lower metal wiring layer;
  - an upper metal wiring layer extending lengthwise in a second lateral direction on the upper insulating film, wherein the second lateral direction is perpendicular to the first lateral direction; and
  - a conductive contact plug passing through the upper insulating film in a vertical direction, the conductive contact plug contacting each of the lower metal wiring layer and the upper metal wiring layer,
    - wherein the conductive contact plug has a tetragonal shape in a view from above,
    - the conductive contact plug comprises a pair of first contact sidewalls, which are opposite to each other in the first lateral direction, and a pair of second contact sidewalls, which are opposite to each other in the second lateral direction,
    - each of the pair of first contact sidewalls extends in the vertical direction from an upper line sidewall of the upper metal wiring layer to the lower metal wiring layer, and
    - at least one of the pair of second contact sidewalls extends in a direction inclined with respect to the vertical direction from a bottom surface of the upper metal wiring layer toward the lower metal wiring layer.
2. The integrated circuit device of claim 1, wherein the upper metal wiring layer and the conductive contact plug have a same width in the first lateral direction,

- a width of each of the upper metal wiring layer and the conductive contact plug in the first lateral direction is constant in the vertical direction, and
- a width of the conductive contact plug gradually reduces toward the lower metal wiring layer in the second lateral direction.
3. The integrated circuit device of claim 1, wherein, in a view from above,
- each of the pair of first contact sidewalls of the conductive contact plug extends along an extension line of a first straight line, along which the upper line sidewall of the upper metal wiring layer in the first lateral direction extends, and
  - each of the pair of second contact sidewalls of the conductive contact plug extends along an extension line of a second straight line, along which a lower line sidewall of the lower metal wiring layer in the second lateral direction extends.
4. The integrated circuit device of claim 1, wherein, in a view from above, a planar shape of the conductive contact plug is same as a planar shape of a region where the lower metal wiring layer overlaps the upper metal wiring layer in the vertical direction.
5. The integrated circuit device of claim 1, wherein the conductive contact plug comprises a main contact portion covering a top surface of the lower metal wiring layer and a protruding contact portion covering a sidewall of the lower metal wiring layer, the protruding contact portion being between the lower metal wiring layer and the lower insulating film.
6. The integrated circuit device of claim 1, wherein, in a view from above,
- each of the pair of first contact sidewalls of the conductive contact plug extends in an extension line of a first straight line, along which the upper line sidewall of the upper metal wiring layer extends in the second lateral direction, and
  - each of the pair of second contact sidewalls of the conductive contact plug extends in an extension line of a second straight line, which extends in the first lateral direction, at a position shifted, in a selected one of the second lateral direction and a direction opposite to the second lateral direction, by a first distance greater than 0 from a lower line sidewall of the lower metal wiring layer, the lower line sidewall of the lower metal wiring layer extending in the first lateral direction.
7. The integrated circuit device of claim 1, wherein the conductive contact plug is integrally connected to the upper metal wiring layer.
8. The integrated circuit device of claim 1, further comprising:
- an etch stop film between the lower insulating film and the upper insulating film,
  - wherein a portion of the conductive contact plug passes through the etch stop film.
9. An integrated circuit device comprising:
- a lower insulating film on a substrate;
  - a first lower metal wiring layer and a second lower metal wiring layer each passing through the lower insulating film and extending lengthwise in a first lateral direction, the first lower metal wiring layer and the second lower metal wiring layer being apart from each other in a second lateral direction, the second lateral direction being perpendicular to the first lateral direction,
  - an upper insulating film on each of the lower insulating film, the first lower metal wiring layer, and the second lower metal wiring layer;
  - a first upper metal wiring layer and a second upper metal wiring layer on the upper insulating film, the first upper metal wiring layer and the second upper metal wiring layer overlapping the first lower metal wiring layer and the second lower metal wiring layer in a vertical direction and extending lengthwise in the second lateral direction, and the first upper metal wiring layer and the second upper metal wiring layer being apart from each other in the first lateral direction;
  - a first conductive contact plug passing through the upper insulating film in the vertical direction, the first conductive contact plug contacting each of the first lower metal wiring layer and the first upper metal wiring layer; and
  - a second conductive contact plug passing through the upper insulating film in the vertical direction, the second conductive contact plug contacting each of the second lower metal wiring layer and the second upper metal wiring layer,
- wherein each of the first conductive contact plug and the second conductive contact plug has a tetragonal shape in a view from above,
- each of the first conductive contact plug and the second conductive contact plug comprises a pair of first contact sidewalls and a pair of second contact sidewalls, the pair of first contact sidewalls being opposite to each other in the first lateral direction, the pair of second contact sidewalls being opposite to each other in the second lateral direction,
- in each of the first conductive contact plug and the second conductive contact plug, each of the pair of first contact sidewalls extends in the vertical direction from a corresponding one of a pair of upper line sidewalls of a corresponding one of the first and second upper metal wiring layers extending in the second lateral direction to a corresponding one of the first and second lower metal wiring layers, and,
- in each of the first conductive contact plug and the second conductive contact plug, at least one of the pair of second contact sidewalls extends in a direction inclined with respect to the vertical direction from a bottom surface of a corresponding one of the first and second upper metal wiring layers toward the corresponding one of the first and second lower metal wiring layers.
10. The integrated circuit device of claim 9, wherein
- a width of each of the first conductive contact plug and the second conductive contact plug in the first lateral direction is constant in the vertical direction, and
  - a width of each of the first conductive contact plug and the second conductive contact plug in the second lateral direction gradually reduces toward the substrate.
11. The integrated circuit device of claim 9, wherein, in a view from above, in each of the first conductive contact plug and the second conductive contact plug,
- each of the pair of first contact sidewalls extends along an extension line of a first straight line, along which a corresponding one of the upper line sidewalls of the corresponding one of the first and second upper metal wiring layers extends, and,
  - each of the pair of second contact sidewalls extends along an extension line of a second straight line, along which

a corresponding one of lower line sidewalls of the corresponding one of the first and second lower metal wiring layers extends.

**12.** The integrated circuit device of claim 9, wherein, in a view from above,

a planar shape of the first conductive contact plug is a same as a planar shape of a region where the first lower metal wiring layer overlaps the first upper metal wiring layer in the vertical direction, and

a planar shape of the second conductive contact plug is same as a planar shape of a region where the second lower metal wiring layer overlaps the second upper metal wiring layer in the vertical direction.

**13.** The integrated circuit device of claim 9, wherein at least one of the first conductive contact plug or the second conductive contact plug covers a top surface and a sidewall of a corresponding one of the first and second lower metal wiring layers.

**14.** The integrated circuit device of claim 9, wherein, in a view from above, in each of the first conductive contact plug and the second conductive contact plug,

each of the pair of first contact sidewalls extends along an extension line of a first straight line, along which a corresponding one of the upper line sidewalls of the corresponding one of the first and second upper metal wiring layers extends, and,

the pair of second contact sidewalls extend in an extension line of a second straight line at a position shifted, in a direction selected from the second lateral direction and a direction opposite to the second lateral direction, by a first distance greater than 0 from a lower line sidewall of a corresponding one of the first and second lower metal wiring layers, the lower line sidewall of a corresponding one of the first and second lower metal wiring layers extending in the first lateral direction.

**15.** The integrated circuit device of claim 9, wherein, in a view from above, in each of the first conductive contact plug and the second conductive contact plug,

each of the pair of first contact sidewalls extends along an extension line of a first straight line, along which a corresponding one of the upper line sidewalls of the corresponding one of the first and second upper metal wiring layers passes,

each of the pair of second contact sidewalls of the first conductive contact plug extends along an extension line of a second straight line, which extends in the first lateral direction, at a position shifted, in a direction opposite to the second lateral direction, by a first distance greater than 0 from a corresponding one of first lower line sidewalls of the first lower metal wiring layer, and

each of the pair of second contact sidewalls of the second conductive contact plug extends along an extension line of a third straight line, which extends in the first lateral direction, at a position shifted, in the second lateral direction, by a second distance greater than 0 from a corresponding one of second lower line sidewalls of the second lower metal wiring layer.

**16.** The integrated circuit device of claim 9, wherein the first conductive contact plug is integrally connected to the first upper metal wiring layer, and the second conductive contact plug is integrally connected to the second upper metal wiring layer.

**17.** The integrated circuit device of claim 9, further comprising:

an etch stop film between the lower insulating film and the upper insulating film,

wherein a portion of each of the first and second conductive contact plugs passes through the etch stop film.

**18.** An integrated circuit device comprising:

a lower structure on a substrate;

a lower insulating film on the lower structure;

a lower metal wiring layer passing through the lower insulating film and extending lengthwise in a first lateral direction;

an upper insulating film on the lower insulating film and the lower metal wiring layer, the upper insulating film defining a line space and a via space connected to the line space, the via space extending from the line space to the lower metal wiring layer in a vertical direction; an upper metal wiring layer filling the line space, the upper metal wiring layer extending lengthwise in a second lateral direction, the second lateral direction being perpendicular to the first lateral direction; and

a conductive contact plug filling the via space and contacting each of the lower metal wiring layer and the upper metal wiring layer,

wherein the upper metal wiring layer comprises a portion extending from a top surface of the upper insulating film to a top surface of the conductive contact plug in the vertical direction,

the conductive contact plug has a tetragonal shape in a view from above,

the conductive contact plug comprises a pair of first contact sidewalls and a pair of second contact sidewalls, the pair of first contact sidewalls being opposite to each other in the first lateral direction and facing the upper insulating film, the pair of second contact sidewalls being opposite to each other in the second lateral direction and facing the upper insulating film,

each of the pair of first contact sidewalls extends in the vertical direction from a corresponding one upper line sidewall adjacent thereto, from among a pair of upper line sidewalls included in the upper metal wiring layer, to the lower metal wiring layer, the pair of upper line sidewalls being opposite to each other in the first lateral direction, and

at least one of the pair of second contact sidewalls extends in a direction inclined with respect to the vertical direction from a bottom surface of the upper metal wiring layer toward the lower metal wiring layer.

**19.** The integrated circuit device of claim 18, wherein the upper metal wiring layer and the conductive contact plug have a same width in the first lateral direction,

a width of each of the upper metal wiring layer and the conductive contact plug in the first lateral direction is constant in the vertical direction, and

a width of the conductive contact plug gradually reduces toward the lower metal wiring layer in the second lateral direction.

**20.** The integrated circuit device of claim 18, wherein a width of each of the upper metal wiring layer and the conductive contact plug in the first lateral direction is constant in the vertical direction, and

in a view from above, the pair of first contact sidewalls of the conductive contact plug extend along extension

lines of a pair of first straight lines, along which the pair of upper line sidewalls of the upper metal wiring layer extend, respectively.

**21.-40.** (canceled)

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